

TENTATIVE TOSHIBA MULTI-CHIP INTEGRATED CIRCUIT SILICON GATE CMOS

SRAM AND FLASH MEMORY MIXED MULTI-CHIP PACKAGE

DESCRIPTION

The TH50VSF4682/4683AASB is a mixed multi-chip package containing a 16,777,216-bit Full CMOS SRAM and a 67,108,864-bit flash memory. The CIOS and CIOF inputs can be used to select the optimal memory configuration. FLASH MEMORY a Simultaneous Read/Write operation so that data can be read during a Write or Erase operation. The TH50VSF4682/4683AASB can range from 2.7 V to 3.1 V. The TH50VSF4682/4683AASB is available in a 69-pin BGA package, making it suitable for a variety of design applications.

FEATURES

- Power supply voltage
 $V_{CCs} = 2.7\text{ V} \sim 3.1\text{ V}$
 $V_{CCf} = 2.7\text{ V} \sim 3.1\text{ V}$
- Data retention supply voltage
 $V_{CCs} = 1.5\text{ V} \sim 3.1\text{ V}$
- Current consumption
 Operating: 45 mA maximum (CMOS level)
 Standby: 10 μA maximum (SRAM CMOS level)
 Standby: 10 μA maximum (FLASH)
- Block erase architecture for flash memory
 8 \times 8 Kbytes
 63 \times 64 Kbytes
- Organization

CIOF	CIOS	Flash Memory	SRAM
V_{CC}	V_{CC}	4,194,304 words of 16 bits	1,048,576 words of 16 bits
V_{CC}	V_{SS}	4,194,304 words of 16 bits	2,097,152 words of 8 bits
V_{SS}	V_{SS}	8,388,608 words of 8 bits	2,097,152 words of 8 bits

- Function mode control for flash memory
 Compatible with JEDEC-standard commands
- Flash memory functions
 Simultaneous Read/Write operations
 Auto-Program
 Auto Chip Erase, Auto Block Erase
 Auto Multiple-Block Erase
 Program Suspend/Resume
 Block-Erase Suspend/Resume
 Data Polling/Toggle Bit function
 Block Protection/Boot Block Protection
 Automatic Sleep, Hidden ROM Area Supports
 Common Flash Memory Interface (CFI)
 Byte/Word Mode
- Erase and Program cycle for flash memory
 10^5 cycles (typical)
- Boot block architecture for flash memory
 TH50VSF4682AASB: Top boot block
 TH50VSF4683AASB: Bottom boot block
- Package
 P-FBGA69-1012-0.80A3: 0.31 g (typ.)

PIN ASSIGNMENT (TOP VIEW)

- Case: CIOF = V_{CC} , CIOS = $V_{CC} (\times 16, \times 16)$

	1	2	3	4	5	6	7	8	9	10
A	NC									NC
B	NC									NC
C	NC		A7	$\overline{\text{LB}}$	$\overline{\text{WP/ACC}}$	$\overline{\text{WE}}$	A8	A11		
D		A3	A6	$\overline{\text{UB}}$	$\overline{\text{RESET}}$	CE2S	A19	A12	A15	
E		A2	A5	A18	RY/ $\overline{\text{BY}}$	A20	A9	A13	A21	
F	NC	A1	A4	A17			A10	A14	NC	NC
G	NC	A0	V_{SS}	DQ1			DQ6	DU	A16	NC
H		$\overline{\text{CEF}}$	$\overline{\text{OE}}$	DQ9	DQ3	DQ4	DQ13	DQ15	CIOF	
J		$\overline{\text{CE1S}}$	DQ0	DQ10	V_{CCf}	V_{CCs}	DQ12	DQ7	V_{SS}	
K			DQ8	DQ2	DQ11	CIOS	DQ5	DQ14		
L	NC									NC
M	NC									NC

PIN NAMES

A0~A22	Address Inputs
A12S	A12 Input for SRAM
A12F	A12 Input for Flash Memory
SA	A20 Input for SRAM
DQ0~DQ15	Data Inputs/Outputs
$\overline{\text{CE1S}}$, CE2S	Chip Enable Inputs for SRAM
$\overline{\text{CEF}}$	Chip Enable Input for Flash Memory
$\overline{\text{OE}}$	Output Enable Input
$\overline{\text{WE}}$	Write Enable Input
$\overline{\text{LB}}$, $\overline{\text{UB}}$	Data Byte Control Input
RY/ $\overline{\text{BY}}$	Ready/Busy Output
$\overline{\text{RESET}}$	Hardware Reset Input
WP/ACC	Write Protect/Program Acceleration Input
CIOS	Word Enable Input for SRAM
CIOF	Word Enable Input for Flash Memory
V_{CCs}	Power Supply for SRAM
V_{CCf}	Power Supply for Flash Memory
V_{SS}	Ground
NC	Not Connected
DU	Don't Use

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PIN ASSIGNMENT (TOP VIEW)

- Case: CIOF = V_{CC}, CIOS = V_{SS} (×16, ×8)

	1	2	3	4	5	6	7	8	9	10
A	NC									NC
B	NC									NC
C	NC		A7	DU	$\overline{WP/ACC}$	\overline{WE}	A8	A11		
D		A3	A6	DU	\overline{RESET}	CE2S	A19	A12	A15	
E		A2	A5	A18	RY/BY	A20	A9	A13	A21	
F	NC	A1	A4	A17			A10	A14	NC	NC
G	NC	A0	V _{SS}	DQ1			DQ6	SA	A16	NC
H		\overline{CEF}	\overline{OE}	DQ9	DQ3	DQ4	DQ13	DQ15	CIOF	
J		$\overline{CE1S}$	DQ0	DQ10	V _{CCf}	V _{CCs}	DQ12	DQ7	V _{SS}	
K			DQ8	DQ2	DQ11	CIOS	DQ5	DQ14		
L	NC									NC
M	NC									NC

- Case: CIOF = V_{SS}, CIOS = V_{SS} (×8, ×8)

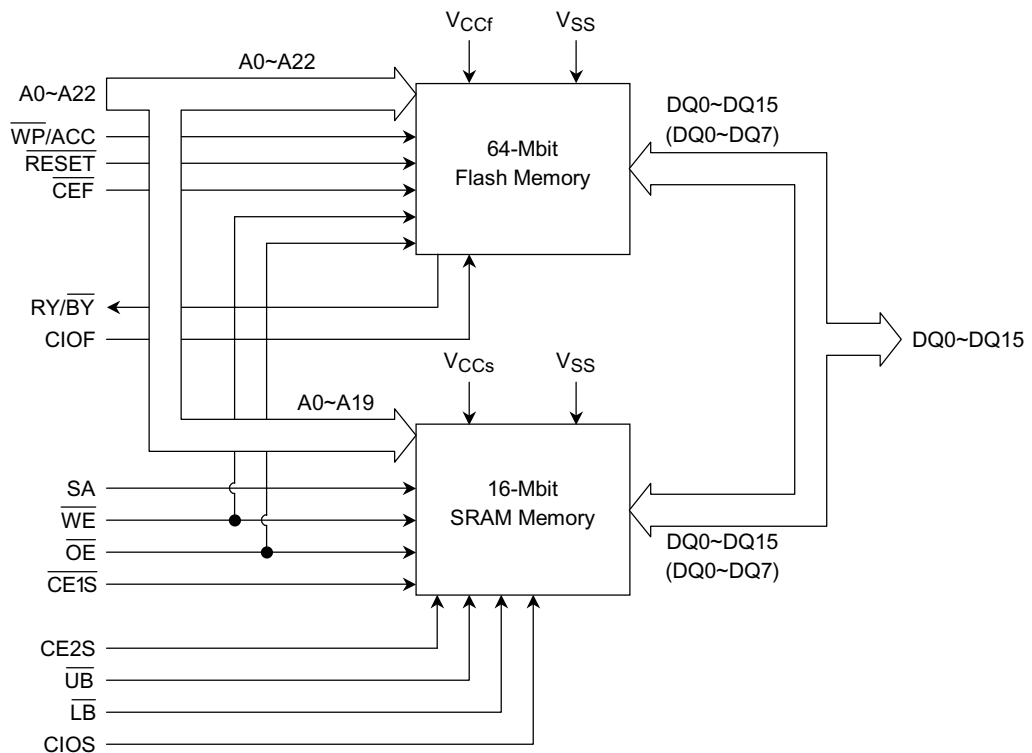
	1	2	3	4	5	6	7	8	9	10
A	NC									NC
B	NC									NC
C	NC		A7	DU	$\overline{WP/ACC}$	\overline{WE}	A8	A11		
D		A3	A6	DU	\overline{RESET}	CE2S	A20	A13	A16	
E		A2	A5	A19	RY/BY	A21	A9	A14	A22	
F	NC	A1	A4	A18			A10	A15	NC	NC
G	NC	A0	V _{SS}	DQ1			DQ6	A12S	A17	NC
H		\overline{CEF}	\overline{OE}	DU	DQ3	DQ4	DU	A12F	CIOF	
J		$\overline{CE1S}$	DQ0	DU	V _{CCf}	V _{CCs}	DU	DQ7	V _{SS}	
K			DU	DQ2	DU	CIOS	DQ5	DU		
L	NC									NC
M	NC									NC

Note: A12F and A12S should be wired and used as A12 pin.

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BLOCK DIAGRAM



MODE SELECTION

OPERATION MODE	$\overline{\text{CEF}}$	$\overline{\text{CE1S}}$	CE2S	$\overline{\text{OE}}$	$\overline{\text{WE}}$	$\overline{\text{RESET}}$	$\overline{\text{UB}}$	$\overline{\text{LB}}$	$\overline{\text{WP/ACC}}$	DQ0-DQ7	DQ8-DQ15
Flash Read	L	H	X	L	H	H	X	X	X	D _{OUT}	D _{OUT}
	L	X	L	L	H	H	X	X	X	D _{OUT}	D _{OUT}
SRAM Read	H	L	H	L	H	H	L	L	X	D _{OUT}	D _{OUT}
	H	L	H	L	H	H	H	L	X	D _{OUT}	Hi-Z
	H	L	H	L	H	H	L	H	X	Hi-Z	D _{OUT}
Flash Write	L	H	X	H	L	H	X	X	X	D _{IN}	D _{IN}
	L	X	L	H	L	H	X	X	X	D _{IN}	D _{IN}
SRAM Write	H	L	H	X	L	H	L	L	X	D _{IN}	D _{IN}
	H	L	H	X	L	H	H	L	X	D _{IN}	Hi-Z
	H	L	H	X	L	H	L	H	X	Hi-Z	D _{IN}
Flash Output Disable	X	H	X	H	H	X	X	X	X	Hi-Z	Hi-Z
	X	X	L	H	H	X	X	X	X	Hi-Z	Hi-Z
SRAM Output Disable	H	X	X	H	H	X	X	X	X	Hi-Z	Hi-Z
	H	X	X	X	X	X	H	H	X	Hi-Z	Hi-Z
Flash Standby	H	X	X	X	X	H	X	X	X	S	S
Flash Hardware Reset / Standby	X	X	X	X	X	L	X	X	X	S	S
SRAM Standby	X	H	X	X	X	X	X	X	X	F	F
	X	X	L	X	X	X	X	X	X	F	F

Notes: L = V_{IL}; H = V_{IH}; X = V_{IH} or V_{IL}

F: Depends on flash memory operation mode. S: Depends on SRAM operation mode.

When CIOS = V_{CC} and CIOF = V_{CC}, Word Mode is selected for both SRAM and flash memory.

Does not apply when $\overline{\text{CEF}} = \overline{\text{CE1S}} = \text{V}_{\text{IL}}$ and CE2S = V_{IH} at the same time.

ID CODE TABLE

TYPE		A21~A12	A6	A1	A0	CODE (HEX) ⁽¹⁾
Manufacturer Code		*	L	L	L	0098H
Device Code	TH50VSF4682AASB	*	L	L	H	0093H
	TH50VSF4683AASB	*	L	L	H	0095H
Verify Block Protect		BA ⁽²⁾	L	H	L	Data ⁽³⁾

Note: * = V_{IH} or V_{IL}

L = V_{IL} H = V_{IH}

(1) DQ8~DQ14 are Hi-Z in Byte mode

A12F: Address input

(2) BA: Block address

(3) 0001H: Protected block

0000H: Unprotected block

COMMAND SEQUENCES

COMMAND SEQUENCE	BUS WRITE CYCLES REQ'D	FIRST BUS WRITE CYCLE		SECOND BUS WRITE CYCLE		THIRD BUS WRITE CYCLE		FOURTH BUS WRITE CYCLE		FIFTH BUS WRITE CYCLE		SIXTH BUS WRITE CYCLE		
		Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	
Read/Reset	1	XXXH	F0H											
Read/Reset	Word	3	555H	AAH	2AAH	55H	555H	F0H	RA ⁽¹⁾	RD ⁽²⁾				
	Byte		AAAH		555H		AAAH							
ID Read	Word	3	555H	AAH	2AAH	55H	BK ⁽³⁾ + 555H	90H	IA ⁽⁴⁾	ID ⁽⁵⁾				
	Byte		AAAH		555H		BK ⁽³⁾ + AAHA							
Auto-Program	Word	4	555H	AAH	2AAH	55H	555H	A0H	PA ⁽⁶⁾	PD ⁽⁷⁾				
	Byte		AAAH		555H		AAAH							
Program Suspend	1	BK ⁽³⁾	B0H											
Program Resume	1	BK ⁽³⁾	30H											
Auto Chip Erase	Word	6	555H	AAH	2AAH	55H	555H	80H	555H	AAH	2AAH	55H	555H	10H
	Byte		AAAH		555H		AAAH		555H		AAAH			
Auto Block Erase	Word	6	555H	AAH	2AAH	55H	555H	80H	555H	AAH	2AAH	55H	BA ⁽⁸⁾	30H
	Byte		AAAH		555H		AAAH		555H		AAAH			
Block Erase Suspend	1	BK ⁽³⁾	B0H											
Block Erase Resume	1	BK ⁽³⁾	30H											
Block Protect	4	XXXH	60H	BPA ⁽⁹⁾	60H	XXXH	40H	BPA ⁽⁹⁾	BPD ⁽¹⁰⁾					
Verify Block Protect	Word	3	555H	AAH	2AAH	55H	BK ⁽³⁾ + 555H	90H	BPA ⁽⁹⁾	BPD ⁽¹⁰⁾				
	Byte		AAAH		555H		BK ⁽³⁾ + AAHA							
Fast Program Set	Word	3	555H	AAH	2AAH	55H	555H	20H						
	Byte		AAAH		555H		AAAH							
Fast Program	2	XXXH	A0H	PA ⁽⁶⁾	PD ⁽⁷⁾									
Fast Program Reset	2	XXXH	90H	XXXH	F0H ⁽¹³⁾									
Hidden ROM Mode Entry	Word	3	555H	AAH	2AAH	55H	555H	88H						
	Byte		AAAH		555H		AAAH							
Hidden ROM Program	Word	4	555H	AAH	2AAH	55H	555H	A0H	PA ⁽⁶⁾	PD ⁽⁷⁾				
	Byte		AAAH		555H		AAAH							
Hidden ROM Erase	Word	6	555H	AAH	2AAH	55H	555H	80H	555H	AAH	2AAH	55H	BA ⁽⁸⁾	30H
	Byte		AAAH		555H		AAAH		555H		AAAH			
Hidden ROM Mode Exit	Word	4	555H	AAH	2AAH	55H	555H	90H	XXXH	00H				
	Byte		AAAH		555H		AAAH							
Query Command	Word	2	BK ⁽³⁾ + 55H	98H	CA ⁽¹¹⁾	CD ⁽¹²⁾								
	Byte		BK ⁽³⁾ + AAHA											

Note: The system should generate the following address patterns:

- Word Mode: 555H or 2AAH to addresses A10~A0
- Byte Mode: AAHA or 555H to addresses A10~A0, A12F
- DQ8~DQ15 are ignored in Word mode.
- Byte mode when V_{IL} is inputted to CIOF, and addresses are A22~A0
- Write mode when V_{IH} is inputted to CIOF, and addresses are A21~A0
- Valid addresses are A10~A0 when a command is entered.

- | | |
|-------------------------------------------------------|---------------------------------------------------------|
| (1) RA: Read Address | (6) PA: Program Address |
| (2) RD: Read Data | (7) PD: Program Data |
| (3) BK: Bank Address = A21~A15 | (8) BA: Block Address = A21~A12 |
| (4) IA: Bank Address and ID Read Address (A6, A1, A0) | (9) BPA: Block Address and ID Read Address (A6, A1, A0) |
| Bank Address = A21~A15 | Block Address = A21~A12 |
| Manufacturer Code = (0, 0, 0) | ID Read Address = (0, 1, 0) |
| Device Code = (0, 0, 1) | (10) BPD: Verify Data |
| (5) ID: ID Data | (11) CA: CFI Address |
| 0098H - Manufacturer Code | (12) CD: CFI Data |
| 0093H - Device Code (TH50VSF4682AASB) | (13) F0H: 00H is valid too |
| 0095H - Device Code (TH50VSF4683AASB) | |
| 0001H - Protected Block | |

BLOCK ERASE ADDRESS TABLES

(1) TH50VSF4682AASB (top boot block)

BANK #	BLOCK #	BLOCK ADDRESS										ADDRESS RANGE		
		BANK ADDRESS								A14	A13	A12	BYTE MODE	WORD MODE
		A21	A20	A19	A18	A17	A16	A15	A14					
BK0	BA0	L	L	L	L	L	L	L	*	*	*	000000H~00FFFFFFH	000000H~007FFFFH	
	BA1	L	L	L	L	L	L	H	*	*	*	010000H~01FFFFFFH	008000H~00FFFFFFH	
	BA2	L	L	L	L	L	H	L	*	*	*	020000H~02FFFFFFH	010000H~017FFFFH	
	BA3	L	L	L	L	L	H	H	*	*	*	030000H~03FFFFFFH	018000H~01FFFFFFH	
	BA4	L	L	L	L	H	L	L	*	*	*	040000H~04FFFFFFH	020000H~027FFFFH	
	BA5	L	L	L	L	H	L	H	*	*	*	050000H~05FFFFFFH	028000H~02FFFFFFH	
	BA6	L	L	L	L	H	H	L	*	*	*	060000H~06FFFFFFH	030000H~037FFFFH	
BK1	BA7	L	L	L	L	H	H	H	*	*	*	070000H~07FFFFFFH	038000H~03FFFFFFH	
	BA8	L	L	L	H	L	L	L	*	*	*	080000H~08FFFFFFH	040000H~047FFFFH	
	BA9	L	L	L	H	L	L	H	*	*	*	090000H~09FFFFFFH	048000H~04FFFFFFH	
	BA10	L	L	L	H	L	H	L	*	*	*	0A0000H~0AFFFFFFH	050000H~057FFFFH	
	BA11	L	L	L	H	L	H	H	*	*	*	0B0000H~0BFFFFFFH	058000H~05FFFFFFH	
	BA12	L	L	L	H	H	L	L	*	*	*	0C0000H~0CFFFFFFH	060000H~067FFFFH	
	BA13	L	L	L	H	H	L	H	*	*	*	0D0000H~0DFFFFFFH	068000H~06FFFFFFH	
BK2	BA14	L	L	L	H	H	H	L	*	*	*	0E0000H~0EFFFFFFH	070000H~077FFFFH	
	BA15	L	L	L	H	H	H	H	*	*	*	0F0000H~0FFFFFFFH	078000H~07FFFFFFH	
	BA16	L	L	H	L	L	L	L	*	*	*	100000H~10FFFFFFH	080000H~087FFFFH	
	BA17	L	L	H	L	L	L	H	*	*	*	110000H~11FFFFFFH	088000H~08FFFFFFH	
	BA18	L	L	H	L	L	H	L	*	*	*	120000H~12FFFFFFH	090000H~097FFFFH	
	BA19	L	L	H	L	L	H	H	*	*	*	130000H~13FFFFFFH	098000H~097FFFFH	
	BA20	L	L	H	L	H	L	L	*	*	*	140000H~14FFFFFFH	0A0000H~0A7FFFFH	
BK3	BA21	L	L	H	L	H	L	H	*	*	*	150000H~15FFFFFFH	0A8000H~0AFFFFFFH	
	BA22	L	L	H	L	H	H	L	*	*	*	160000H~16FFFFFFH	0B0000H~0B7FFFFH	
	BA23	L	L	H	L	H	H	H	*	*	*	170000H~17FFFFFFH	0B8000H~0BFFFFFFH	
	BA24	L	L	H	H	L	L	L	*	*	*	180000H~18FFFFFFH	0C0000H~0C7FFFFH	
	BA25	L	L	H	H	L	L	H	*	*	*	190000H~19FFFFFFH	0C8000H~0CFFFFFFH	
	BA26	L	L	H	H	L	H	L	*	*	*	1A0000H~1AFFFFFFH	0D0000H~0D7FFFFH	
	BA27	L	L	H	H	L	H	H	*	*	*	1B0000H~1BFFFFFFH	0D8000H~0DFFFFFFH	
BK3	BA28	L	L	H	H	H	L	L	*	*	*	1C0000H~1CFFFFFFH	0E0000H~0E7FFFFH	
	BA29	L	L	H	H	H	L	H	*	*	*	1D0000H~1DFFFFFFH	0E8000H~0EFFFFFFH	
	BA30	L	L	H	H	H	H	L	*	*	*	1E0000H~1EFFFFFFH	0F0000H~0F7FFFFH	
	BA31	L	L	H	H	H	H	H	*	*	*	1F0000H~1FFFFFFFH	0F8000H~0FFFFFFFH	

(Continued)

BANK #	BLOCK #	BLOCK ADDRESS										ADDRESS RANGE	
		BANK ADDRESS										BYTE MODE	WORD MODE
		A21	A20	A19	A18	A17	A16	A15	A14	A13	A12		
BK4	BA32	L	H	L	L	L	L	L	*	*	*	200000H~20FFFFH	100000H~107FFFH
	BA33	L	H	L	L	L	L	H	*	*	*	210000H~21FFFFH	108000H~10FFFFH
	BA34	L	H	L	L	L	H	L	*	*	*	220000H~22FFFFH	110000H~117FFFH
	BA35	L	H	L	L	L	H	H	*	*	*	230000H~23FFFFH	118000H~11FFFFH
	BA36	L	H	L	L	H	L	L	*	*	*	240000H~24FFFFH	120000H~127FFFH
	BA37	L	H	L	L	H	L	H	*	*	*	250000H~25FFFFH	128000H~12FFFFH
	BA38	L	H	L	L	H	H	L	*	*	*	260000H~26FFFFH	130000H~137FFFH
	BA39	L	H	L	L	H	H	H	*	*	*	270000H~27FFFFH	138000H~13FFFFH
BK5	BA40	L	H	L	H	L	L	L	*	*	*	280000H~28FFFFH	140000H~147FFFH
	BA41	L	H	L	H	L	L	H	*	*	*	290000H~29FFFFH	148000H~14FFFFH
	BA42	L	H	L	H	L	H	L	*	*	*	2A0000H~2AFFFFH	150000H~157FFFH
	BA43	L	H	L	H	L	H	H	*	*	*	2B0000H~2BFFFFH	158000H~15FFFFH
	BA44	L	H	L	H	H	L	L	*	*	*	2C0000H~2CFFFFH	160000H~167FFFH
	BA45	L	H	L	H	H	L	H	*	*	*	2D0000H~2DFFFFH	168000H~16FFFFH
	BA46	L	H	L	H	H	H	L	*	*	*	2E0000H~2EFFFFH	170000H~177FFFH
	BA47	L	H	L	H	H	H	H	*	*	*	2F0000H~2FFFFFH	178000H~17FFFFH
BK6	BA48	L	H	H	L	L	L	L	*	*	*	300000H~30FFFFH	180000H~187FFFH
	BA49	L	H	H	L	L	L	H	*	*	*	310000H~31FFFFH	188000H~18FFFFH
	BA50	L	H	H	L	L	H	L	*	*	*	320000H~32FFFFH	190000H~197FFFH
	BA51	L	H	H	L	L	H	H	*	*	*	330000H~33FFFFH	198000H~19FFFFH
	BA52	L	H	H	L	H	L	L	*	*	*	340000H~34FFFFH	1A0000H~1A7FFFH
	BA53	L	H	H	L	H	L	H	*	*	*	350000H~35FFFFH	1A8000H~1AFFFFH
	BA54	L	H	H	L	H	H	L	*	*	*	360000H~36FFFFH	1B0000H~1B7FFFH
	BA55	L	H	H	L	H	H	H	*	*	*	370000H~37FFFFH	1B8000H~1BFFFFH
BK7	BA56	L	H	H	H	L	L	L	*	*	*	380000H~38FFFFH	1C0000H~1C7FFFH
	BA57	L	H	H	H	L	L	H	*	*	*	390000H~39FFFFH	1C8000H~1CFFFFH
	BA58	L	H	H	H	L	H	L	*	*	*	3A0000H~3AFFFFH	1D0000H~1D7FFFH
	BA59	L	H	H	H	L	H	H	*	*	*	3B0000H~3BFFFFH	1D8000H~1DFFFFH
	BA60	L	H	H	H	H	L	L	*	*	*	3C0000H~3CFFFFH	1E0000H~1E7FFFH
	BA61	L	H	H	H	H	L	H	*	*	*	3D0000H~3DFFFFH	1E8000H~1EFFFFH
	BA62	L	H	H	H	H	H	L	*	*	*	3E0000H~3EFFFFH	1F0000H~1F7FFFH
	BA63	L	H	H	H	H	H	H	*	*	*	3F0000H~3FFFFFH	1F8000H~1FFFFFH

(Continued)

BANK #	BLOCK #	BLOCK ADDRESS										ADDRESS RANGE		
		BANK ADDRESS								A14	A13	A12	BYTE MODE	WORD MODE
		A21	A20	A19	A18	A17	A16	A15						
BK8	BA64	H	L	L	L	L	L	L	*	*	*	400000H~40FFFFH	200000H~207FFFH	
	BA65	H	L	L	L	L	L	H	*	*	*	410000H~41FFFFH	208000H~20FFFFH	
	BA66	H	L	L	L	L	H	L	*	*	*	420000H~42FFFFH	210000H~217FFFH	
	BA67	H	L	L	L	L	H	H	*	*	*	430000H~43FFFFH	218000H~21FFFFH	
	BA68	H	L	L	L	H	L	L	*	*	*	440000H~44FFFFH	220000H~227FFFH	
	BA69	H	L	L	L	H	L	H	*	*	*	450000H~45FFFFH	228000H~22FFFFH	
	BA70	H	L	L	L	H	H	L	*	*	*	460000H~46FFFFH	230000H~237FFFH	
	BA71	H	L	L	L	H	H	H	*	*	*	470000H~47FFFFH	238000H~23FFFFH	
BK9	BA72	H	L	L	H	L	L	L	*	*	*	480000H~48FFFFH	240000H~247FFFH	
	BA73	H	L	L	H	L	L	H	*	*	*	490000H~49FFFFH	248000H~24FFFFH	
	BA74	H	L	L	H	L	H	L	*	*	*	4A0000H~4AFFFFH	250000H~257FFFH	
	BA75	H	L	L	H	L	H	H	*	*	*	4B0000H~4BFFFFH	258000H~25FFFFH	
	BA76	H	L	L	H	H	L	L	*	*	*	4C0000H~4CFFFFH	260000H~267FFFH	
	BA77	H	L	L	H	H	L	H	*	*	*	4D0000H~4DFFFFH	268000H~26FFFFH	
	BA78	H	L	L	H	H	H	L	*	*	*	4E0000H~4EFFFFH	270000H~277FFFH	
	BA79	H	L	L	H	H	H	H	*	*	*	4F0000H~4FFFFFH	278000H~27FFFFH	
BK10	BA80	H	L	H	L	L	L	L	*	*	*	500000H~50FFFFH	280000H~287FFFH	
	BA81	H	L	H	L	L	L	H	*	*	*	510000H~51FFFFH	288000H~28FFFFH	
	BA82	H	L	H	L	L	H	L	*	*	*	520000H~52FFFFH	290000H~297FFFH	
	BA83	H	L	H	L	L	H	H	*	*	*	530000H~53FFFFH	298000H~29FFFFH	
	BA84	H	L	H	L	H	L	L	*	*	*	540000H~54FFFFH	2A0000H~2A7FFFH	
	BA85	H	L	H	L	H	L	H	*	*	*	550000H~55FFFFH	2A8000H~2AFFFFH	
	BA86	H	L	H	L	H	H	L	*	*	*	560000H~56FFFFH	2B0000H~2B7FFFH	
	BA87	H	L	H	L	H	H	H	*	*	*	570000H~57FFFFH	2B8000H~2BFFFFH	
BK11	BA88	H	L	H	H	L	L	L	*	*	*	580000H~58FFFFH	2C0000H~2C7FFFH	
	BA89	H	L	H	H	L	L	H	*	*	*	590000H~59FFFFH	2C8000H~2CFFFFH	
	BA90	H	L	H	H	L	H	L	*	*	*	5A0000H~5AFFFFH	2D0000H~2D7FFFH	
	BA91	H	L	H	H	L	H	H	*	*	*	5B0000H~5BFFFFH	2D8000H~2DFFFFH	
	BA92	H	L	H	H	H	L	L	*	*	*	5C0000H~5CFFFFH	2E0000H~2E7FFFH	
	BA93	H	L	H	H	H	L	H	*	*	*	5D0000H~5DFFFFH	2E8000H~2EFFFFH	
	BA94	H	L	H	H	H	H	L	*	*	*	5E0000H~5EFFFFH	2F0000H~2F7FFFH	
	BA95	H	L	H	H	H	H	H	*	*	*	5F0000H~5FFFFFH	2F8000H~2FFFFFH	

(Continued)

BANK #	BLOCK #	BLOCK ADDRESS										ADDRESS RANGE	
		BANK ADDRESS										BYTE MODE	WORD MODE
		A21	A20	A19	A18	A17	A16	A15	A14	A13	A12		
BK12	BA96	H	H	L	L	L	L	L	*	*	*	600000H~60FFFFH	300000H~307FFFH
	BA97	H	H	L	L	L	L	H	*	*	*	610000H~61FFFFH	308000H~30FFFFH
	BA98	H	H	L	L	L	H	L	*	*	*	620000H~62FFFFH	310000H~317FFFH
	BA99	H	H	L	L	L	H	H	*	*	*	630000H~63FFFFH	318000H~31FFFFH
	BA100	H	H	L	L	H	L	L	*	*	*	640000H~64FFFFH	320000H~327FFFH
	BA101	H	H	L	L	H	L	H	*	*	*	650000H~65FFFFH	328000H~32FFFFH
	BA102	H	H	L	L	H	H	L	*	*	*	660000H~66FFFFH	330000H~337FFFH
	BA103	H	H	L	L	H	H	H	*	*	*	670000H~67FFFFH	338000H~33FFFFH
BK13	BA104	H	H	L	H	L	L	L	*	*	*	680000H~68FFFFH	340000H~347FFFH
	BA105	H	H	L	H	L	L	H	*	*	*	690000H~69FFFFH	348000H~34FFFFH
	BA106	H	H	L	H	L	H	L	*	*	*	6A0000H~6AFFFFH	350000H~357FFFH
	BA107	H	H	L	H	L	H	H	*	*	*	6B0000H~6BFFFFH	358000H~35FFFFH
	BA108	H	H	L	H	H	L	L	*	*	*	6C0000H~6CFFFFH	360000H~367FFFH
	BA109	H	H	L	H	H	L	H	*	*	*	6D0000H~6DFFFFH	368000H~36FFFFH
	BA110	H	H	L	H	H	H	L	*	*	*	6E0000H~6EFFFFH	370000H~377FFFH
	BA111	H	H	L	H	H	H	H	*	*	*	6F0000H~6FFFFFH	378000H~37FFFFH
BK14	BA112	H	H	H	L	L	L	L	*	*	*	700000H~70FFFFH	380000H~387FFFH
	BA113	H	H	H	L	L	L	H	*	*	*	710000H~71FFFFH	388000H~38FFFFH
	BA114	H	H	H	L	L	H	L	*	*	*	720000H~72FFFFH	390000H~397FFFH
	BA115	H	H	H	L	L	H	H	*	*	*	730000H~73FFFFH	398000H~39FFFFH
	BA116	H	H	H	L	H	L	L	*	*	*	740000H~74FFFFH	3A0000H~3A7FFFH
	BA117	H	H	H	L	H	L	H	*	*	*	770000H~75FFFFH	3A8000H~3AFFFFH
	BA118	H	H	H	L	H	H	L	*	*	*	760000H~76FFFFH	3B0000H~3B7FFFH
	BA119	H	H	H	L	H	H	H	*	*	*	770000H~77FFFFH	3B8000H~3BFFFFH
BK15	BA120	H	H	H	H	L	L	L	*	*	*	780000H~78FFFFH	3C0000H~3C7FFFH
	BA121	H	H	H	H	L	L	H	*	*	*	790000H~79FFFFH	3C8000H~3CFFFFH
	BA122	H	H	H	H	L	H	L	*	*	*	7A0000H~7AFFFFH	3D0000H~3D7FFFH
	BA123	H	H	H	H	L	H	H	*	*	*	7B0000H~7BFFFFH	3D8000H~3DFFFFH
	BA124	H	H	H	H	H	L	L	*	*	*	7C0000H~7CFFFFH	3E0000H~3E7FFFH
	BA125	H	H	H	H	H	L	H	*	*	*	7D0000H~7DFFFFH	3E8000H~3EFFFFH
	BA126	H	H	H	H	H	H	L	*	*	*	7E0000H~7EFFFFH	3F0000H~3F7FFFH

(Continued)

BANK #	BLOCK #	BLOCK ADDRESS										ADDRESS RANGE	
		BANK ADDRESS										BYTE MODE	WORD MODE
		A21	A20	A19	A18	A17	A16	A15	A14	A13	A12		
BK16	BA127	H	H	H	H	H	H	H	L	L	L	7F0000H~7F1FFFH	3F8000H~3F8FFFH
	BA128	H	H	H	H	H	H	H	L	L	H	7F2000H~7F3FFFH	3F9000H~3F9FFFH
	BA129	H	H	H	H	H	H	H	L	H	L	7F4000H~7F5FFFH	3FA000H~3FAFFFH
	BA130	H	H	H	H	H	H	H	L	H	H	7F6000H~7F7FFFH	3FB000H~3FBFFFH
	BA131	H	H	H	H	H	H	H	H	L	L	7F8000H~7F9FFFH	3FC000H~3FCFFFH
	BA132	H	H	H	H	H	H	H	H	L	H	7FA000H~7FBFFFH	3FD000H~3FDFFFH
	BA133	H	H	H	H	H	H	H	H	H	L	7FC000H~7FDFFFH	3FE000H~3FEFFFH
	BA134	H	H	H	H	H	H	H	H	H	H	7FE000H~7FFFFFFH	3FF000H~3FFFFFFH

(2) TH50VSF4683AASB (bottom boot block)

BANK #	BLOCK #	BLOCK ADDRESS										ADDRESS RANGE			
		BANK ADDRESS								A14	A13	A12	BYTE MODE	WORD MODE	
		A21	A20	A19	A18	A17	A16	A15	A14						
BK0	BA0	L	L	L	L	L	L	L	L	L	L	L	L	000000H~001FFFFH	000000H~000FFFFH
	BA1	L	L	L	L	L	L	L	L	L	L	L	H	002000H~003FFFFH	001000H~001FFFFH
	BA2	L	L	L	L	L	L	L	L	L	H	L	L	004000H~005FFFFH	002000H~002FFFFH
	BA3	L	L	L	L	L	L	L	L	L	H	H	L	006000H~007FFFFH	003000H~003FFFFH
	BA4	L	L	L	L	L	L	L	L	H	L	L	L	008000H~009FFFFH	004000H~004FFFFH
	BA5	L	L	L	L	L	L	L	L	H	L	H	L	00A000H~00BFFFFH	005000H~005FFFFH
	BA6	L	L	L	L	L	L	L	L	H	H	L	L	00C000H~00DFFFFH	006000H~006FFFFH
	BA7	L	L	L	L	L	L	L	L	H	H	H	L	00E000H~00FFFFFFH	007000H~007FFFFH
BK1	BA8	L	L	L	L	L	L	H	*	*	*	L	L	010000H~01FFFFFFH	008000H~00FFFFFFH
	BA9	L	L	L	L	L	H	L	*	*	*	L	L	020000H~02FFFFFFH	010000H~017FFFFH
	BA10	L	L	L	L	L	H	H	*	*	*	L	L	030000H~03FFFFFFH	018000H~01FFFFFFH
	BA11	L	L	L	L	H	L	L	*	*	*	L	L	040000H~04FFFFFFH	020000H~027FFFFH
	BA12	L	L	L	L	H	L	H	*	*	*	L	L	050000H~05FFFFFFH	028000H~02FFFFFFH
	BA13	L	L	L	L	H	H	L	*	*	*	L	L	060000H~06FFFFFFH	030000H~037FFFFH
	BA14	L	L	L	L	H	H	H	*	*	*	L	L	070000H~07FFFFFFH	038000H~03FFFFFFH
BK2	BA15	L	L	L	H	L	L	L	*	*	*	L	L	080000H~08FFFFFFH	040000H~047FFFFH
	BA16	L	L	L	H	L	L	H	*	*	*	L	L	090000H~09FFFFFFH	048000H~04FFFFFFH
	BA17	L	L	L	H	L	H	L	*	*	*	L	L	0A0000H~0AFFFFFFH	050000H~057FFFFH
	BA18	L	L	L	H	L	H	H	*	*	*	L	L	0B0000H~0BFFFFFFH	058000H~05FFFFFFH
	BA19	L	L	L	H	H	L	L	*	*	*	L	L	0C0000H~0CFFFFFFH	060000H~067FFFFH
	BA20	L	L	L	H	H	L	H	*	*	*	L	L	0D0000H~0DFFFFFFH	068000H~06FFFFFFH
	BA21	L	L	L	H	H	H	L	*	*	*	L	L	0E0000H~0EFFFFFFH	070000H~077FFFFH
	BA22	L	L	L	H	H	H	H	*	*	*	L	L	0F0000H~0FFFFFFFH	078000H~07FFFFFFH
BK3	BA23	L	L	H	L	L	L	L	*	*	*	L	L	100000H~10FFFFFFH	080000H~087FFFFH
	BA24	L	L	H	L	L	L	H	*	*	*	L	L	110000H~11FFFFFFH	088000H~08FFFFFFH
	BA25	L	L	H	L	L	H	L	*	*	*	L	L	120000H~12FFFFFFH	090000H~097FFFFH
	BA26	L	L	H	L	L	H	H	*	*	*	L	L	130000H~13FFFFFFH	098000H~09FFFFFFH
	BA27	L	L	H	L	H	L	L	*	*	*	L	L	140000H~14FFFFFFH	0A0000H~0A7FFFFH
	BA28	L	L	H	L	H	L	H	*	*	*	L	L	150000H~15FFFFFFH	0A8000H~0AFFFFFFH
	BA29	L	L	H	L	H	H	L	*	*	*	L	L	160000H~16FFFFFFH	0B0000H~0B7FFFFH
	BA30	L	L	H	L	H	H	H	*	*	*	L	L	170000H~17FFFFFFH	0B8000H~0BFFFFFFH

(Continued)

BANK #	BLOCK #	BLOCK ADDRESS										ADDRESS RANGE	
		BANK ADDRESS							A14	A13	A12	BYTE MODE	WORD MODE
		A21	A20	A19	A18	A17	A16	A15					
BK4	BA31	L	L	H	H	L	L	L	*	*	*	180000H~18FFFFH	0C0000H~0C7FFFH
	BA32	L	L	H	H	L	L	H	*	*	*	190000H~19FFFFH	0C8000H~0CFFFFH
	BA33	L	L	H	H	L	H	L	*	*	*	1A0000H~1AFFFFH	0D0000H~0D7FFFH
	BA34	L	L	H	H	L	H	H	*	*	*	1B0000H~1BFFFFH	0D8000H~0DFFFFH
	BA35	L	L	H	H	H	L	L	*	*	*	1C0000H~1CFFFFH	0E0000H~0E7FFFH
	BA36	L	L	H	H	H	L	H	*	*	*	1D0000H~1DFFFFH	0E8000H~0EFFFFH
	BA37	L	L	H	H	H	H	L	*	*	*	1E0000H~1EFFFFH	0F0000H~0F7FFFH
	BA38	L	L	H	H	H	H	H	*	*	*	1F0000H~1FFFFFH	0F8000H~0FFFFFH
BK5	BA39	L	H	L	L	L	L	L	*	*	*	200000H~20FFFFH	100000H~107FFFH
	BA40	L	H	L	L	L	L	H	*	*	*	210000H~21FFFFH	108000H~10FFFFH
	BA41	L	H	L	L	L	H	L	*	*	*	220000H~22FFFFH	110000H~117FFFH
	BA42	L	H	L	L	L	H	H	*	*	*	230000H~23FFFFH	118000H~11FFFFH
	BA43	L	H	L	L	H	L	L	*	*	*	240000H~24FFFFH	120000H~127FFFH
	BA44	L	H	L	L	H	L	H	*	*	*	250000H~25FFFFH	128000H~12FFFFH
	BA45	L	H	L	L	H	H	L	*	*	*	260000H~26FFFFH	130000H~137FFFH
	BA46	L	H	L	L	H	H	H	*	*	*	270000H~27FFFFH	138000H~13FFFFH
BK6	BA47	L	H	L	H	L	L	L	*	*	*	280000H~28FFFFH	140000H~147FFFH
	BA48	L	H	L	H	L	L	H	*	*	*	290000H~29FFFFH	148000H~14FFFFH
	BA49	L	H	L	H	L	H	L	*	*	*	2A0000H~2AFFFFH	150000H~157FFFH
	BA50	L	H	L	H	L	H	H	*	*	*	2B0000H~2BFFFFH	158000H~15FFFFH
	BA51	L	H	L	H	H	L	L	*	*	*	2C0000H~2CFFFFH	160000H~167FFFH
	BA52	L	H	L	H	H	L	H	*	*	*	2D0000H~2DFFFFH	168000H~16FFFFH
	BA53	L	H	L	H	H	H	L	*	*	*	2E0000H~2EFFFFH	170000H~177FFFH
	BA54	L	H	L	H	H	H	H	*	*	*	2F0000H~2FFFFFH	178000H~17FFFFH
BK7	BA55	L	H	H	L	L	L	L	*	*	*	300000H~30FFFFH	180000H~187FFFH
	BA56	L	H	H	L	L	L	H	*	*	*	310000H~31FFFFH	188000H~18FFFFH
	BA57	L	H	H	L	L	H	L	*	*	*	320000H~32FFFFH	190000H~197FFFH
	BA58	L	H	H	L	L	H	H	*	*	*	330000H~33FFFFH	198000H~19FFFFH
	BA59	L	H	H	L	H	L	L	*	*	*	340000H~34FFFFH	1A0000H~1A7FFFH
	BA60	L	H	H	L	H	L	H	*	*	*	350000H~35FFFFH	1A8000H~1AFFFFH
	BA61	L	H	H	L	H	H	L	*	*	*	360000H~36FFFFH	1B0000H~1B7FFFH
	BA62	L	H	H	L	H	H	H	*	*	*	370000H~37FFFFH	1B8000H~1BFFFFH

(Continued)

BANK #	BLOCK #	BLOCK ADDRESS										ADDRESS RANGE	
		BANK ADDRESS										BYTE MODE	WORD MODE
		A21	A20	A19	A18	A17	A16	A15	A14	A13	A12		
BK8	BA63	L	H	H	H	L	L	L	*	*	*	380000H~38FFFFH	1C0000H~1C7FFFH
	BA64	L	H	H	H	L	L	H	*	*	*	390000H~39FFFFH	1C8000H~1CFFFFH
	BA65	L	H	H	H	L	H	L	*	*	*	3A0000H~3AFFFFH	1D0000H~1D7FFFH
	BA66	L	H	H	H	L	H	H	*	*	*	3B0000H~3BFFFFH	1D8000H~1DFFFFH
	BA67	L	H	H	H	H	L	L	*	*	*	3C0000H~3CFFFFH	1E0000H~1E7FFFH
	BA68	L	H	H	H	H	L	H	*	*	*	3D0000H~3DFFFFH	1E8000H~1EFFFFH
	BA69	L	H	H	H	H	H	L	*	*	*	3E0000H~3EFFFFH	1F0000H~1F7FFFH
	BA70	L	H	H	H	H	H	H	*	*	*	3F0000H~3FFFFFH	1F8000H~1FFFFFH
BK9	BA71	H	L	L	L	L	L	L	*	*	*	400000H~40FFFFH	200000H~207FFFH
	BA72	H	L	L	L	L	L	H	*	*	*	410000H~41FFFFH	208000H~20FFFFH
	BA73	H	L	L	L	L	H	L	*	*	*	420000H~42FFFFH	210000H~217FFFH
	BA74	H	L	L	L	L	H	H	*	*	*	430000H~43FFFFH	218000H~21FFFFH
	BA75	H	L	L	L	H	L	L	*	*	*	440000H~44FFFFH	220000H~227FFFH
	BA76	H	L	L	L	H	L	H	*	*	*	450000H~45FFFFH	228000H~22FFFFH
	BA77	H	L	L	L	H	H	L	*	*	*	460000H~46FFFFH	230000H~237FFFH
	BA78	H	L	L	L	H	H	H	*	*	*	470000H~47FFFFH	238000H~23FFFFH
BK10	BA79	H	L	L	H	L	L	L	*	*	*	480000H~48FFFFH	240000H~247FFFH
	BA80	H	L	L	H	L	L	H	*	*	*	490000H~49FFFFH	248000H~24FFFFH
	BA81	H	L	L	H	L	H	L	*	*	*	4A0000H~4AFFFFH	250000H~257FFFH
	BA82	H	L	L	H	L	H	H	*	*	*	4B0000H~4BFFFFH	258000H~25FFFFH
	BA83	H	L	L	H	H	L	L	*	*	*	4C0000H~4CFFFFH	260000H~267FFFH
	BA84	H	L	L	H	H	L	H	*	*	*	4D0000H~4DFFFFH	268000H~26FFFFH
	BA85	H	L	L	H	H	H	L	*	*	*	4E0000H~4EFFFFH	270000H~277FFFH
	BA86	H	L	L	H	H	H	H	*	*	*	4F0000H~4FFFFFH	278000H~27FFFFH
BK11	BA87	H	L	H	L	L	L	L	*	*	*	500000H~50FFFFH	280000H~287FFFH
	BA88	H	L	H	L	L	L	H	*	*	*	510000H~51FFFFH	288000H~28FFFFH
	BA89	H	L	H	L	L	H	L	*	*	*	520000H~52FFFFH	290000H~297FFFH
	BA90	H	L	H	L	L	H	H	*	*	*	530000H~53FFFFH	298000H~29FFFFH
	BA91	H	L	H	L	H	L	L	*	*	*	540000H~54FFFFH	2A0000H~2A7FFFH
	BA92	H	L	H	L	H	L	H	*	*	*	550000H~55FFFFH	2A8000H~2AFFFFH
	BA93	H	L	H	L	H	H	L	*	*	*	560000H~56FFFFH	2B0000H~2B7FFFH
	BA94	H	L	H	L	H	H	H	*	*	*	570000H~57FFFFH	2B8000H~2BFFFFH

(Continued)

BANK #	BLOCK #	BLOCK ADDRESS										ADDRESS RANGE	
		BANK ADDRESS										BYTE MODE	WORD MODE
		A21	A20	A19	A18	A17	A16	A15	A14	A13	A12		
BK12	BA95	H	L	H	H	L	L	L	*	*	*	580000H~58FFFFFFH	2C0000H~2C7FFFFH
	BA96	H	L	H	H	L	L	H	*	*	*	590000H~59FFFFFFH	2C8000H~2CFFFFFFH
	BA97	H	L	H	H	L	H	L	*	*	*	5A0000H~5AFFFFFFH	2D0000H~2D7FFFFH
	BA98	H	L	H	H	L	H	H	*	*	*	5B0000H~5BFFFFFFH	2D8000H~2DFFFFFFH
	BA99	H	L	H	H	H	L	L	*	*	*	5C0000H~5CFFFFFFH	2E0000H~2E7FFFFH
	BA100	H	L	H	H	H	L	H	*	*	*	5D0000H~5DFFFFFFH	2E8000H~2EFFFFFFH
	BA101	H	L	H	H	H	H	L	*	*	*	5E0000H~5EFFFFFFH	2F0000H~2F7FFFFH
	BA102	H	L	H	H	H	H	H	*	*	*	5F0000H~5FFFFFFH	2F8000H~2FFFFFFH
BK13	BA103	H	H	L	L	L	L	L	*	*	*	600000H~60FFFFFFH	300000H~307FFFFH
	BA104	H	H	L	L	L	L	H	*	*	*	610000H~61FFFFFFH	308000H~30FFFFFFH
	BA105	H	H	L	L	L	H	L	*	*	*	620000H~62FFFFFFH	310000H~317FFFFH
	BA106	H	H	L	L	L	H	H	*	*	*	630000H~63FFFFFFH	318000H~31FFFFFFH
	BA107	H	H	L	L	H	L	L	*	*	*	640000H~64FFFFFFH	320000H~327FFFFH
	BA108	H	H	L	L	H	L	H	*	*	*	650000H~65FFFFFFH	328000H~32FFFFFFH
	BA109	H	H	L	L	H	H	L	*	*	*	660000H~66FFFFFFH	330000H~337FFFFH
	BA110	H	H	L	L	H	H	H	*	*	*	670000H~67FFFFFFH	338000H~33FFFFFFH
BK14	BA111	H	H	L	H	L	L	L	*	*	*	680000H~68FFFFFFH	340000H~347FFFFH
	BA112	H	H	L	H	L	L	H	*	*	*	690000H~69FFFFFFH	348000H~34FFFFFFH
	BA113	H	H	L	H	L	H	L	*	*	*	6A0000H~6AFFFFFFH	350000H~357FFFFH
	BA114	H	H	L	H	L	H	H	*	*	*	6B0000H~6BFFFFFFH	358000H~35FFFFFFH
	BA115	H	H	L	H	H	L	L	*	*	*	6C0000H~6CFFFFFFH	360000H~367FFFFH
	BA116	H	H	L	H	H	L	H	*	*	*	6D0000H~6DFFFFFFH	368000H~36FFFFFFH
	BA117	H	H	L	H	H	H	L	*	*	*	6E0000H~6EFFFFFFH	370000H~377FFFFH
	BA118	H	H	L	H	H	H	H	*	*	*	6F0000H~6FFFFFFH	378000H~37FFFFFFH
BK15	BA119	H	H	H	L	L	L	L	*	*	*	700000H~70FFFFFFH	380000H~387FFFFH
	BA120	H	H	H	L	L	L	H	*	*	*	710000H~71FFFFFFH	388000H~38FFFFFFH
	BA121	H	H	H	L	L	H	L	*	*	*	720000H~72FFFFFFH	390000H~397FFFFH
	BA122	H	H	H	L	L	H	H	*	*	*	730000H~73FFFFFFH	398000H~39FFFFFFH
	BA123	H	H	H	L	H	L	L	*	*	*	740000H~74FFFFFFH	3A0000H~3A7FFFFH
	BA124	H	H	H	L	H	L	H	*	*	*	750000H~75FFFFFFH	3A8000H~3AFFFFFFH
	BA125	H	H	H	L	H	H	L	*	*	*	760000H~76FFFFFFH	3B0000H~3B7FFFFH
	BA126	H	H	H	L	H	H	H	*	*	*	770000H~77FFFFFFH	3B8000H~3BFFFFFFH

(Continued)

BANK #	BLOCK #	BLOCK ADDRESS										ADDRESS RANGE			
		BANK ADDRESS									A14	A13	A12	BYTE MODE	WORD MODE
		A21	A20	A19	A18	A17	A16	A15							
BK16	BA127	H	H	H	H	L	L	L	*	*	*	780000H~78FFFFH	3C0000H~3C7FFFH		
	BA128	H	H	H	H	L	L	H	*	*	*	790000H~79FFFFH	3C8000H~3CFFFFH		
	BA129	H	H	H	H	L	H	L	*	*	*	7A0000H~7AFFFFH	3D0000H~3D7FFFH		
	BA130	H	H	H	H	L	H	H	*	*	*	7B0000H~7BFFFFH	3D8000H~3DFFFFH		
	BA131	H	H	H	H	H	L	L	*	*	*	7C0000H~7CFFFFH	3E0000H~3E7FFFH		
	BA132	H	H	H	H	H	L	H	*	*	*	7D0000H~7DFFFFH	3E8000H~3EFFFFH		
	BA133	H	H	H	H	H	H	L	*	*	*	7E0000H~7EFFFFH	3F0000H~3F7FFFH		
	BA134	H	H	H	H	H	H	H	*	*	*	7FE000H~7FFFFFFH	3F8000H~3FFFFFFH		

BLOCK SIZE TABLE

(1) TH50VSF4682AASB (top boot block)

BLOCK #	BLOCK SIZE		BANK #	BANK SIZE		BLOCK COUNT
	BYTE MODE	WORD MODE		BYTE MODE	WORD MODE	
BA0~BA7	64 Kbytes	32 Kwords	BK0	512 Kbytes	256 Kwords	8
BA8~BA15	64 Kbytes	32 Kwords	BK1	512 Kbytes	256 Kwords	8
BA16~BA23	64 Kbytes	32 Kwords	BK2	512 Kbytes	256 Kwords	8
BA24~BA31	64 Kbytes	32 Kwords	BK3	512 Kbytes	256 Kwords	8
BA32~BA39	64 Kbytes	32 Kwords	BK4	512 Kbytes	256 Kwords	8
BA40~BA47	64 Kbytes	32 Kwords	BK5	512 Kbytes	256 Kwords	8
BA48~BA55	64 Kbytes	32 Kwords	BK6	512 Kbytes	256 Kwords	8
BA56~BA63	64 Kbytes	32 Kwords	BK7	512 Kbytes	256 Kwords	8
BA64~BA71	64 Kbytes	32 Kwords	BK8	512 Kbytes	256 Kwords	8
BA72~BA79	64 Kbytes	32 Kwords	BK9	512 Kbytes	256 Kwords	8
BA80~BA87	64 Kbytes	32 Kwords	BK10	512 Kbytes	256 Kwords	8
BA88~BA95	64 Kbytes	32 Kwords	BK11	512 Kbytes	256 Kwords	8
BA96~BA103	64 Kbytes	32 Kwords	BK12	512 Kbytes	256 Kwords	8
BA104~BA111	64 Kbytes	32 Kwords	BK13	512 Kbytes	256 Kwords	8
BA112~BA119	64 Kbytes	32 Kwords	BK14	512 Kbytes	256 Kwords	8
BA120~BA126	64 Kbytes	32 Kwords	BK15	448 Kbytes	224 Kwords	7
BA127~BA134	8 Kbytes	4 Kwords	BK16	64 Kbytes	32 Kwords	8

(2) TH50VSF4683AASB (bottom boot block)

BLOCK #	BLOCK SIZE		BANK #	BANK SIZE		BLOCK COUNT
	BYTE MODE	WORD MODE		BYTE MODE	WORD MODE	
BA0~BA7	8 Kbytes	4 Kwords	BK0	64 Kbytes	32 Kwords	8
BA8~BA14	64 Kbytes	32 Kwords	BK1	448 Kbytes	224 Kwords	7
BA15~BA22	64 Kbytes	32 Kwords	BK2	512 Kbytes	256 Kwords	8
BA23~BA30	64 Kbytes	32 Kwords	BK3	512 Kbytes	256 Kwords	8
BA31~BA38	64 Kbytes	32 Kwords	BK4	512 Kbytes	256 Kwords	8
BA39~BA46	64 Kbytes	32 Kwords	BK5	512 Kbytes	256 Kwords	8
BA47~BA54	64 Kbytes	32 Kwords	BK6	512 Kbytes	256 Kwords	8
BA55~BA62	64 Kbytes	32 Kwords	BK7	512 Kbytes	256 Kwords	8
BA63~BA70	64 Kbytes	32 Kwords	BK8	512 Kbytes	256 Kwords	8
BA71~BA78	64 Kbytes	32 Kwords	BK9	512 Kbytes	256 Kwords	8
BA79~BA86	64 Kbytes	32 Kwords	BK10	512 Kbytes	256 Kwords	8
BA87~BA94	64 Kbytes	32 Kwords	BK11	512 Kbytes	256 Kwords	8
BA95~BA102	64 Kbytes	32 Kwords	BK12	512 Kbytes	256 Kwords	8
BA103~BA110	64 Kbytes	32 Kwords	BK13	512 Kbytes	256 Kwords	8
BA111~BA118	64 Kbytes	32 Kwords	BK14	512 Kbytes	256 Kwords	8
BA119~BA126	64 Kbytes	32 Kwords	BK15	512 Kbytes	256 Kwords	8
BA127~BA134	64 Kbytes	32 Kwords	BK16	512 Kbytes	256 Kwords	8

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RANGE	UNIT
V _{CC}	V _{CCs} /V _{CCf} Supply Voltage	-0.3~4.2 ⁽³⁾	V
V _{IN}	Input Voltage ⁽¹⁾	-0.3~4.2	V
V _{DQ}	Input/Output Voltage	-0.5~V _{CC} + 0.5 (≤ 4.2)	V
T _{opr}	Operating Temperature	-30~85	°C
P _D	Power Dissipation	0.6	W
T _{solder}	Soldering Temperature (10 s)	260	°C
I _{OSHORT}	Output Short Circuit Current ⁽²⁾	100	mA
N _{EW}	Erase/Program Cycling Capability	100,000	Cycle
T _{stg}	Storage Temperature	-55~125	°C

(1) -2.0 V for pulse width ≤ 20 ns

(2) Output shorted for no more than one second. No more than one output shorted at a time

(3) The potential difference of V_{CCs} and V_{CCf} is less than 0.5 V

HARDWARE STATUS FLAGS

STATUS			DQ7	DQ6	DQ5	DQ3	DQ2	RY/ $\overline{\text{BY}}$	
In Progress	Auto Programming		$\overline{\text{DQ7}}$	Toggle	0	0	1	0	
	Read in Program Suspend ⁽¹⁾		Data	Data	Data	Data	Data	Hi-Z	
	In Auto-Erase	Erase Hold Time	Selected ⁽²⁾	0	Toggle	0	0	Toggle	0
			Non-Selected ⁽³⁾	0	Toggle	0	0	1	0
		Auto-Erase	Selected	0	Toggle	0	1	Toggle	0
			Non-Selected	0	Toggle	0	1	1	0
	In Erase Suspend	Read	Selected	1	1	0	0	Toggle	Hi-Z
			Non-Selected	Data	Data	Data	Data	Data	Hi-Z
Programming		Selected	$\overline{\text{DQ7}}$	Toggle	0	0	Toggle	0	
		Non-Selected	$\overline{\text{DQ7}}$	Toggle	0	0	1	0	
Time Limit Exceeded	Auto Programming		$\overline{\text{DQ7}}$	Toggle	1	0	1	0	
	Auto-Erase		0	Toggle	1	1	N/A	0	
	Programming in Erase Suspend		$\overline{\text{DQ7}}$	Toggle	1	0	N/A	0	

Notes: DQ outputs cell data and RY/ $\overline{\text{BY}}$ to high impedance when the operation has completed.

DQ0 and DQ1 pins are reserved for future use.

DQ0, DQ1 and DQ4 output 0.

(1) Data output from an address to which Write is being performed are undefined.

(2) Output when the block address selected for Auto Block Erase is specified and data is read from there. During Auto Chip Erase, all blocks are selected.

(3) Output when a block address not selected for Auto Block Erase of same bank as selected block is specified and data is read from there.

RECOMMENDED DC OPERATING CONDITIONS (Ta = -30°~85°C)

SYMBOL	PARAMETER	MIN	TYP.	MAX	UNIT
V _{CCs} /V _{CCf}	Power Supply Voltage	2.7 ⁽²⁾	—	3.1 ⁽²⁾	V
V _{IH}	Input High-Level Voltage	2.2	—	V _{CC} + 0.3	
V _{IL}	Input Low-Level Voltage	-0.3 ⁽¹⁾	—	V _{CC} × 0.22	
V _{DH}	Data Retention Voltage for SRAM	1.5	—	3.1	
V _{LKO}	Flash Low-Lock Voltage	2.3	—	2.5	
V _{ACC}	High Voltage for $\overline{WP/ACC}$	8.5	—	9.5	
V _{ID}	High Voltage for \overline{RESET}	11.4	—	12.6	

(1) -2.0 V for pulse width ≤ 20 ns

(2) The potential difference of V_{CCs} and V_{CCf} is less than 0.5 V

CAPACITANCE (Ta = 25°C, f = 1 MHz)

SYMBOL	PARAMETER	CONDITION	MIN	TYP.	MAX	UNIT
C _{IN}	Input Capacitance	V _{IN} = GND	—	—	15	pF
C _{OUT}	Output Capacitance	V _{OUT} = GND	—	—	20	pF

Note: These parameters are sampled periodically and are not tested for every device.

DC CHARACTERISTICS (Ta = -30~85°C, VCCs/VCCf = 2.7 V~3.1 V)

SYMBOL	PARAMETER	CONDITION	MIN	TYP.	MAX	UNIT	
I _{IL}	Input Leakage Current	V _{IN} = 0 V~V _{CC}	—	—	±1	μA	
I _{SOH}	SRAM Output High Current	V _{OH} = V _{CCs} - 0.5 V	-0.5	—	—	mA	
I _{SOL}	SRAM Output Low Current	V _{OL} = 0.4 V	2.1	—	—	mA	
I _{FOH1}	Flash Output High Current (TTL)	V _{OH} = 2.4 V	-0.4	—	—	mA	
I _{FOH2}	Flash Output High Current (CMOS)	V _{OH} = V _{CCf} × 0.85	-2.5	—	—	mA	
		V _{OH} = V _{CCf} - 0.4 V	-100	—	—	μA	
I _{FOL}	Flash Output Low Current	V _{OL} = 0.4 V	4	—	—	mA	
I _{LO}	Output Leakage Current	V _{OUT} = 0 V~V _{CC} , $\overline{OE} = V_{IH}$	—	—	±1	μA	
I _{CCO1}	Flash Average Read Current	$\overline{CE1S} = V_{IL}$, $\overline{OE} = V_{IH}$, I _{OUT} = 0 mA, t _{cycle} = t _{RC} (min)	—	—	30	mA	
I _{CCO2}	Flash Average Program/Erase Current	$\overline{CE1S} = V_{IL}$, $\overline{OE} = V_{IH}$, I _{OUT} = 0 mA	—	—	15	mA	
I _{CCO3}	SRAM Average Operating Current	$\overline{CE1S} = V_{IL}$, CE2S = V _{IH} , $\overline{OE} = V_{IH}$, I _{OUT} = 0 mA	t _{cycle} = t _{RC}	—	—	50	mA
			t _{cycle} = 1 MHz	—	—	10	
I _{CCO4}	SRAM Average Operating Current	$\overline{CE1S} = 0.2 V$, $\overline{OE} = V_{CCs} - 0.2 V$, CE2S = V _{CCs} - 0.2 V, I _{OUT} = 0 mA	t _{cycle} = t _{RC}	—	—	45	mA
			t _{cycle} = 1 MHz	—	—	5	
I _{CCO5}	Flash Average Read-While-Program Current	V _{IN} = V _{IH} /V _{IL} , I _{OUT} = 0 mA, t _{cycle} = t _{RC} (min)	—	—	45	mA	
I _{CCO6}	Flash Average Read-While-Erase Current	V _{IN} = V _{IH} /V _{IL} , I _{OUT} = 0 mA, t _{cycle} = t _{RC} (min)	—	—	45	mA	
I _{CCO7}	Flash Average Program-While-Erase-Suspend Current	V _{IN} = V _{IH} /V _{IL} , I _{OUT} = 0 mA	—	—	15	mA	
I _{CCS1}	Flash Standby Current	$\overline{CE1S} = \overline{RESET} = V_{CCf}$ or $\overline{RESET} = V_{SS}$	—	—	10	μA	
I _{CCS2}	Flash Standby Current (Automatic Sleep Mode ⁽¹⁾)	V _{IH} = V _{CCf} or V _{IL} = V _{SS}	—	—	10	μA	
I _{CCS3}	SRAM Standby Current	$\overline{CE1S} = V_{IH}$ or CE2S = V _{IL}	—	—	2	mA	
I _{CCS4}		V _{CCs} = 3.1 V	Ta = 25°C	—	—		1
			Ta = -30~85°C	—	—		10
		V _{CCs} = 3.0 V	Ta = 25°C	—	0.01		0.5
			Ta = -30~40°C	—	—		1
Ta = -30~85°C	—	—	5				
I _{ACC}	High Voltage Input Current for WP/ACC	8.5 V ≤ V _{ACC} ≤ 9.5 V	—	—	20	mA	

(1) The device is going to Automatic Sleep Mode, when address remain steady during 150 ns.

(2) In Standby Mode, with $\overline{CE1S} \geq V_{CCs} - 0.2 V$, these limits are guaranteed when CE2S ≥ V_{CCs} - 0.2 V or CE2S ≤ 0.2 V and CIO5 ≥ V_{CCs} - 0.2 V or CIO5 ≤ 0.2 V.

AC CHARACTERISTICS (SRAM) (Ta = -30°~85°C, VCCs = 2.7 V~3.1 V)

Read cycle

SYMBOL	PARAMETER	MIN	MAX	UNIT
t _{RC}	Read Cycle Time	70	—	ns
t _{ACC}	Address Access Time	—	70	
t _{CO1}	Chip Enable (CE1S) Access Time	—	70	
t _{CO2}	Chip Enable (CE2S) Access Time	—	70	
t _{OE}	Output Enable Access Time	—	35	
t _{BA}	Data Byte Control Access Time	—	70	
t _{COE}	Chip Enable Low to Output Active	5	—	
t _{OEE}	Output Enable Low to Output Active	0	—	
t _{BE}	Data Byte Control Low to Output Active	0	—	
t _{OD}	Chip Enable High to Output Hi-Z	—	30	
t _{ODO}	Output Enable High to Output Hi-Z	—	30	
t _{BD}	Data Byte Control High to Output Hi-Z	—	30	
t _{OH}	Output Data Hold Time	10	—	
t _{CCR}	CE Recovery Time	0	—	

Write cycle

SYMBOL	PARAMETER	MIN	MAX	UNIT
t _{WC}	Write Cycle Time	70	—	ns
t _{WP}	Write Pulse Width	50	—	
t _{CW}	Chip Enable to End of Write	60	—	
t _{BW}	Data Byte Control to End of Write	60	—	
t _{AS}	Address Set-up Time	0	—	
t _{WR}	Write Recovery Time	0	—	
t _{ODW}	\overline{WE} Low to Output Hi-Z	—	25	
t _{OEW}	\overline{WE} High to Output Active	0	—	
t _{DS}	Data Set-up Time	30	—	
t _{DH}	Data Hold Time	0	—	

AC TEST CONDITIONS

PARAMETER	VALUES
Input Pulse Level	0.4 V, 2.4 V
Input Pulse Rise and Fall Time (10%~90%)	5 ns
Timing Measurement Reference Level (input)	VCCs × 0.5
Timing Measurement Reference Level (output)	VCCs × 0.5
Output Load	C _L (100 pF) + 1 TTL gate

AC CHARACTERISTICS (FLASH MEMORY)

READ CYCLE

SYMBOL	PARAMETER	LOAD CAPACITANCE				UNIT
		30pF		100pF		
		MIN	MAX	MIN	MAX	
t _{RC}	Read Cycle Time	70	—	—	80	ns
t _{ACC}	Address Access Time	—	70	—	80	ns
t _{CE}	$\overline{\text{CE}}\overline{\text{F}}$ Access Time	—	70	—	80	ns
t _{OE}	$\overline{\text{OE}}$ Access Time	—	30	—	35	ns
t _{CEE}	$\overline{\text{CE}}\overline{\text{F}}$ to Output Lo-Z	0	—	0	—	ns
t _{OEE}	$\overline{\text{OE}}$ to Output Lo-Z	0	—	0	—	ns
t _{OEH}	$\overline{\text{OE}}$ Hold Time	0	—	0	—	ns
t _{OH}	Output Data Hold Time	0	—	0	—	ns
t _{DF1}	$\overline{\text{CE}}\overline{\text{F}}$ to Output Hi-Z	—	25	—	25	ns
t _{DF2}	$\overline{\text{OE}}$ to Output Hi-Z	—	25	—	25	ns

BLOCK PROTECT

SYMBOL	PARAMETER	MIN	MAX	UNIT
t _{VPS}	V _{ID} Set-up Time	4	—	μs
t _{CESP}	$\overline{\text{CE}}\overline{\text{F}}$ Set-up Time	4	—	μs
t _{VPH}	$\overline{\text{OE}}$ Hold Time	4	—	μs
t _{PPLH}	$\overline{\text{WE}}$ Low-Level Hold Time	100	—	μs

PROGRAM AND ERASE CHARACTERISTICS

SYMBOL	PARAMETER	MIN	MAX	UNIT
t _{PPW}	Auto-Program Time (Byte Mode)	8*	300	μs
	Auto-Program Time (Word Mode)	11*	300	μs
t _{PCEW}	Auto Chip Erase Time	95*	1350	s
t _{PBEW}	Auto Block Erase Time	0.7*	10	s
t _{EW}	Erase/Program Cycle	10 ⁵	—	Cyc.

*: typ.

COMMAND WRITE/PROGRAM/ERASE CYCLE

SYMBOL	PARAMETER	LOAD CAPACITANCE				UNIT
		30pF		100pF		
		MIN	MAX	MIN	MAX	
t _{CMD}	Command Write Cycle Time	70	—	80	—	ns
t _{AS}	Address Set-up Time / CIOF Set-up Time	0	—	0	—	ns
t _{AH}	Address Hold Time / CIOF Hold Time	40	—	40	—	ns
t _{AHW}	Address Hold Time from \overline{WE} High level	20	—	20	—	ns
t _{DS}	Data Set-up Time	40	—	40	—	ns
t _{DH}	Data Hold Time	0	—	0	—	ns
t _{WELH}	\overline{WE} Low-Level Hold Time (\overline{WE} Control)	40	—	40	—	ns
t _{WEHH}	\overline{WE} High-Level Hold Time (\overline{WE} Control)	20	—	20	—	ns
t _{CES}	$\overline{CE\overline{F}}$ Set-up Time to \overline{WE} Active (\overline{WE} Control)	0	—	0	—	ns
t _{CEH}	$\overline{CE\overline{F}}$ Hold Time from \overline{WE} High Level (\overline{WE} Control)	0	—	0	—	ns
t _{CELH}	$\overline{CE\overline{F}}$ Low-Level Hold Time ($\overline{CE\overline{F}}$ Control)	40	—	40	—	ns
t _{CEHH}	$\overline{CE\overline{F}}$ High-Level Hold Time ($\overline{CE\overline{F}}$ Control)	20	—	20	—	ns
t _{WES}	\overline{WE} Set-up time to $\overline{CE\overline{F}}$ Active ($\overline{CE\overline{F}}$ Control)	0	—	0	—	ns
t _{WEH}	\overline{WE} Hold Time from High Level ($\overline{CE\overline{F}}$ Control)	0	—	0	—	ns
t _{OES}	\overline{OE} Set-up Time	0	—	0	—	ns
t _{OEHP}	\overline{OE} Hold Time (Toggle/Data Polling)	90	—	90	—	ns
t _{OEHT}	\overline{OE} High-Level Hold Time (Toggle)	20	—	20	—	ns
t _{AST}	Address Set-up Time (Toggle)	0	—	0	—	ns
t _{AHT}	Address Hold Time (Toggle)	0	—	0	—	ns
t _{BEH}	Erase Hold Time	50	—	50	—	μs
t _{VCS}	V _{CCr} Set-up Time	500	—	500	—	μs
t _{BUSY}	Program/Erase-Valid-to-RY/ \overline{BY} Delay	—	90	—	90	ns
t _{RP}	\overline{RESET} Low-Level Hold Time	500	—	500	—	ns
t _{READY}	\overline{RESET} Low-Level to Read Mode	—	20	—	20	μs
t _{RB}	RY/ \overline{BY} Recovery Time	0	—	0	—	ns
t _{RH}	\overline{RESET} Recovery Time	50	—	50	—	ns
t _{CEBTS}	$\overline{CE\overline{F}}$ Set-up time (CIOF control)	5	—	5	—	ns
t _{SUSP}	Program Suspend Command to Suspend Mode	—	1.5	—	1.5	μs
t _{RESP}	Program Resume Command to Program Mode	—	1	—	1	μs
t _{SUSE}	Erase Suspend Command to Suspend Mode	—	15	—	15	μs
t _{RESE}	Erase Resume Command to Erase Mode	—	1	—	1	μs

SIMULTANEOUS READ/WRITE OPERATION

The TH50VSF4682/4683AASB features a Simultaneous Read/Write operation. The Simultaneous Read/Write operation enables the device to simultaneously write data to or erase data from a bank while the device reads data from another bank.

The TH50VSF4682/4683AASB has a total of seventeen banks: 0.5 Mbits × 1 bank, 3.5 Mbits × 1 bank, and 4 Mbits × 15 banks. Banks are switched using bank addresses (A20 to A15). For bank blocks and addresses, refer to the Block Address Table and Block Size Table.

The Simultaneous Read/Write operation cannot perform multiple operations in a bank. The table below shows the operating modes in which simultaneous operation can be performed.

Note that during Auto Program execution or Auto Block Erase operation, the Simultaneous Read/Write operation cannot read data from addresses which are not selected for operation in the same bank. Data from such addresses can be read using the Program Suspend or Erase Suspend function.

SIMULTANEOUS READ/WRITE OPERATION

ONE BANK STATUS	OTHER BANK STATUS
Read mode	Read mode
ID Read mode ⁽¹⁾	
Auto Program mode	
Fast Program mode ⁽²⁾	
Program Suspend mode	
Auto Block Erase mode	
Auto Multiple Block Erase mode ⁽³⁾	
Erase Suspend mode	
Program Suspend while Erase Suspend	
CFI mode	

(1) Command mode only is valid.

(2) Includes when Acceleration mode is in use.

(3) If the selected bank exists in all banks, simultaneous operation is not supported.

OPERATING MODES

In addition to Read, Write, and Erase modes, the TH50VSF4682/4683AASB features many functions including Block Protect and Data Polling. When using the device, reference the timing charts and flow charts together with the description below.

Read Mode

To read data from the memory cell array, set the device to Read mode. In Read mode, the device can perform high-speed random access as asynchronous ROM.

The device is automatically set to Read mode immediately after power on or after completion of automatic operation. A software reset releases ID Read mode and the lock state when automatic operation ends abnormally, and sets to Read mode. A hardware reset terminates operation of the device and resets to Read mode. When reading the data without changing the address immediately after power on, either input a hardware reset or change $\overline{CE\overline{F}}$ from H to L.

ID Read Mode

ID Read mode is used to read the device maker code and device code. The mode is useful for EPROM programmers to automatically identify the device type.

In this method, simultaneous operation can be performed. Inputting an ID Read command sets the specified bank to ID Read mode. Banks are specified by inputting the bank address (BK) in the third bus write cycle of the command cycle. To read an ID code, the bank address as well as the ID read address must be specified. From address BK + 00 the maker code is output; from address BK + 01 the device code is output. From other banks, data are output from the memory cells. Inputting a Reset command releases ID Read mode and returns the device to Read mode.

Access time in ID Read mode is the same as that in Read mode. For the codes, see the ID Code Table.

Standby Mode

There are two methods of entering Standby mode.

- (1) Control using $\overline{CE\overline{F}}$ and $\overline{RESE\overline{T}}$

When the device is in Read mode, input $V_{DD} \pm 0.3$ V to $\overline{CE\overline{F}}$ and $\overline{RESE\overline{T}}$. The device enters Standby mode and the current becomes standby current (I_{CCS1}). However, if the device is in simultaneous operation, the device does not enter Standby mode but causes the operating current to flow.

- (2) Control using only $\overline{RESE\overline{T}}$

When the device is in Read mode, input $V_{SS} \pm 0.3$ V to $\overline{RESE\overline{T}}$. The device enters Standby mode and the current becomes standby current (I_{CCS1}). Even if the device is in simultaneous operation, this method can terminate the current operation and set the device to Standby mode. This is a hardware reset, described later.

In standby mode, DQ is put in high-impedance state.

Auto Sleep Mode

Function which suppresses power dissipation during read. When address input does not change for 150 ns or longer, the device automatically enters Sleep mode and the current becomes standby current (I_{CCS2}). However, if the device is in simultaneous operation, the device does not enter Standby mode but causes the operating current to flow. Because the output data are latched, data are output in Sleep mode. When the address is changed, Sleep mode is automatically released, outputting data from the changed address.

Output Disable Mode

Inputting V_{IH} to \overline{OE} disables output from the device, setting DQ to high-impedance.

Command Write

The TH50VSF4682/4683AASB utilizes the JEDEC command control standard for a single power supply E²PROM. A Command is executed by inputting an address and data into the Command register. The Command is written by inputting a pulse to \overline{WE} with $\overline{CE\overline{F}} = V_{IL}$ and $\overline{OE} = V_{IH}$ (\overline{WE} control). The command can also be written by inputting a pulse to $\overline{CE\overline{F}}$ with $\overline{WE} = V_{IL}$ ($\overline{CE\overline{F}}$ control). The address is latched on the falling edge of either \overline{WE} or $\overline{CE\overline{F}}$. The data is latched on the rising edge of either \overline{WE} or $\overline{CE\overline{F}}$. DQ0 to DQ7 are valid for data input and DQ8 to DQ15 are ignored.

To cancel input of the command sequence mid-way, use the Reset command. The device resets the Command register and enters Read mode. When an undefined command is input, the Command register is reset and the device enters Read mode.

Software Reset

Apply a software reset by inputting a Read/Reset command. Software reset returns the device from ID Read or CFI mode to Read mode, releases the lock state when automatic operation ends abnormally, or clears the Command register.

Hardware Reset

A hardware reset initializes the device and sets it to Read mode. When a pulse is input to \overline{RESET} for t_{RP} , the device ends the operation in progress and enters Read mode after t_{READY} . Note that if a hardware reset is applied during data overwrite such as a Write or Erase operation, data at that address or block become undefined.

After a hardware reset the device enters Read mode when $\overline{RESET} = V_{IH}$ and Standby mode when $\overline{RESET} = V_{IL}$. The DQ pins are High-Impedance when $\overline{RESET} = V_{IL}$. The Read operation sequence and input of any command are allowed after the device enters Read mode.

Comparison with Software Reset and Hardware Reset

ACTION	SOFTWARE RESET	HARDWARE RESET
Release ID Read or CFI mode	Valid	Valid
Clear the Command register	Valid	Valid
Release the lock state when automatic operation ends abnormally	Valid	Valid
Stop automatic operation in progress	Invalid	Valid
All stops of operation other than the above, and return to Read mode	Invalid	Valid

BYTE/WORD Mode

CIOF is used select Word mode (16 bits) or Byte mode (8 bits) for the TH50VSF4682/4683AASB. When V_{IH} is input to CIOF, the device operates in Word mode. Read data or write commands using DQ0 to DQ15. When V_{IL} is input to CIOF, read data or write commands using DQ0 to DQ7. A12F is used as the lowest address. DQ8 to DQ14 become high-impedance.

Auto-Program Mode

The TH50VSF4682/4683AASB can be programmed in either byte or word units. The Auto Program mode is set using the Program command. The program address is latched on the falling edge of the \overline{WE} signal and data is latched on the rising edge of the fourth bus cycle (with \overline{WE} control). Auto programming starts on the rising edge of the \overline{WE} signal in the fourth bus cycle. The Program and Program Verify commands are automatically executed by the chip. The device status during programming is determined from the Hardware Sequence flag. To read the Hardware Sequence flag, specify the address to which Write is being performed.

During Auto Program execution, a command sequence for the bank on which execution is being performed cannot be received. To terminate execution, use a hardware reset. Note that when the operation is terminated, data cannot be correctly written.

Programming of a protected block is ignored. The device enters Read mode 3 μ s after the rising edge of the \overline{WE} signal in the fourth bus cycle.

If an Auto Program operation fails, the device remains in programming state and does not automatically return to Read mode. The device status can be determined from the setting of the Hardware Sequence flag. Either a Reset command or a hardware reset is necessary to return the device to Read mode after a failure. If a programming operation fails, please do not try to use the block which contains the address to which data could not be programmed.

The device allows the programming of memory cells from 1 to 0. The programming of Memory cells from 0 to 1 will fail. At this time, execution of Auto Program fails. This indicates that the failure is due to the usage rather than the device. A cell must be erased to turn it from 0 to 1.

Fast Program Mode

Fast Program is a function which enables execution of the command sequence for the Auto Program in two cycles. In this mode the first two cycles of the command sequence, which normally needs four cycles, are omitted. Write is performed in the remaining two cycles. To execute Fast Program, input the Fast Program set command. Write in this mode uses the Fast Program command but operation is the same as that for ordinary Auto Program. The status of the device can be checked using the hardware sequence flag and read operations can be performed as usual. To exit this mode, the Fast Program Reset command must be input. When the command is input, the device returns to Read mode.

Acceleration Mode

The TH50VSF4682/4683AASB features Acceleration mode for reducing write time. Applying V_{ACC} to \overline{WP} or ACC automatically sets the device to Acceleration mode. In Acceleration mode, Block Protect mode changes to Temporary Block Unprotect mode. Write mode changes to Fast Program mode. Modes are switched by the \overline{WP}/ACC signal; thus, there is no need for a Temporary Block Unprotect operation or for setting or resetting Fast Program mode. Operation of Write is the same as that in Auto Program mode. Releasing V_{ACC} to \overline{WP}/ACC ends Acceleration mode.

Program Suspend / Resume Mode

Program Suspend is used to enable Data Read by suspending Write operation. The device receives a Program Suspend command in Write mode (including Write performed during Erase Suspend) but ignores the command in other modes. At command input, the address of the bank on which Write is being performed must be specified. After command input, the device enters Program Suspend Read mode after tSUSP.

During Program Suspend, Cell Data Read, ID Read and CFI Data Read can be performed. When Data Write is suspended, the address to which Write was being performed becomes undefined. ID Read and CFI Data Read are the same as usual.

After completion of Program Suspend, to return to Write mode, input a Program Resume command. At command input, specify the address of the bank on which Write is being performed. When the ID Read and CFI Data Read functions are used, end the functions before inputting the Resume command. On receiving the Resume command, the device returns to Write mode and resumes output of a Hardware Sequence flag from the bank to which data are being written.

Program Suspend can be run in Fast Program or Acceleration mode. However, note that when running Program Suspend in Acceleration mode, do not release VACC.

Auto Chip Erase Mode

The Auto Chip Erase mode is set using the Chip Erase command. The Auto Chip Erase operation starts on the rising edge of \overline{WE} in the sixth bus cycle. All memory cells are automatically preprogrammed to 0, erased and verified as erased by the chip. The device status is determined from the Hardware Sequence flag.

Command inputs are ignored during an Auto Chip Erase. The hardware reset allows interruption of an Auto Chip Erase operation. The Auto Chip Erase operation does not complete correctly when interrupted. Hence a further Erase operation is necessary.

An attempt to erase a protected block is ignored. If all blocks are protected, the Auto Erase operation will not be executed and the device will enter Read mode 100 μ s after the rising edge of the \overline{WE} signal in the sixth bus cycle.

If an Auto Chip Erase operation fails, the device remains in, erasing state and does not return to Read mode. The device status is determined from the Hardware Sequence flag. Either a Reset command or a hardware reset is necessary to return the device to Read mode after a failure.

In this case, the block in which a failure occurred cannot be detected. Either terminate device usage, or perform Block Erase for each block, specify the failed block, and stop using it. The host processor must take measures to prevent use of the failed block being used in the future.

Auto Block / Multiple Block Erase Mode

The Auto Block and Multiple Block Erase modes are set using the Block Erase command. The block address is latched on the falling edge of the \overline{WE} signal in the sixth bus cycle. The Block Erase starts as soon as the erase hold time (t_{BEH}) has elapsed after the rising edge of the \overline{WE} signal. To erase multiple blocks, repeat the 6th bus write cycles and input the block addresses and the Auto Block Erase command within the erase hold time (Auto Multiple Block Erase). If a command sequence other than Auto Block Erase or Erase Suspend command is input during the erase hold time, the device resets the Command register and enters Read mode. The erase hold time is valid every \overline{WE} rising edge. Once operation starts, all the memory cells in the block selected in the device are automatically preprogrammed to data 0, erased, and Erase is verified. The device status can be determined from the setting of the Hardware Sequence flag. To read the Hardware Sequence flag, the addresses of blocks on which Auto Erase is being performed must be specified. When the selected blocks exit in all the banks, simultaneous operation cannot be performed.

Commands (except Erase Suspend) are ignored during a Block/Multiple Block Erase operation. The operation can be aborted by a hardware reset. The Auto Erase operation does not complete correctly when aborted, therefore, a further Erase operation is necessary.

An attempt to erase a protected block is ignored. If all the selected blocks are protected, the Auto Erase operation is not executed and the device returns to Read mode 100 μ s after the rising edge of the \overline{WE} signal in the last bus cycle.

If an Auto Erase operation fails, the device remains in erasing state and does not return to Read mode. The device status is determined from the Hardware Sequence flag. Either a Reset command or a Hardware reset is necessary to return the device to Read mode after a failure. If multiple blocks are selected, the block in which a failure occurred cannot be detected. Either terminate device usage, or perform Block Erase for each block, specify the failed block, and stop using it. The host processor must take measures to prevent use of the failed block being used in the future.

Erase Suspend / Resume Mode

Erase Suspend Mode suspends Auto Block Erase and reads data from or writes data to an unselected block. The Erase Suspend command is allowed during an auto block erase operation but is ignored in all other operation modes. The Erase Suspend command is inhibited to input during the Erase Hold Time. When the command is input, the address of the bank on which Erase is being performed must be specified.

In Erase Suspend Mode only a Read, Program or Resume command can be accepted. If an Erase Suspend command is input during an Auto Block Erase, the device will enter Erase Suspend Read Mode after t_{SUSE} . The device status (Erase Suspend Read Mode) can be verified by checking the Hardware Sequence flag. If data is read consecutively from the block selected for Auto Block Erase, the DQ2 output will toggle and the DQ6 output will stop toggling and $\overline{RY/BY}$ will be set to High-Impedance.

Inputting a Write command during an Erase Suspend enables a Write to be performed to a block which has not been selected for the Auto Block Erase. Data is written in the usual manner.

To resume the Auto Block Erase, input an Erase Resume command. On input of the command, the address of the bank on which the Write was being performed must be specified. On receiving an Erase Resume command, the device returns to the state it was in when the Erase Suspend command was input. If an Erase Suspend command is input during the Erase Hold Time, the device will return to the state it was in at the start of the Erase Hold Time. At this time more blocks can be specified for erasing. If an Erase Resume command is input during an Auto Block Erase, Erase resumes. At this time toggle output of DQ6 resumes and 0 is output on $\overline{RY/BY}$.

Block Protect

Block Protection is a function to disable write and erase in block units. Applying VID to $\overline{\text{RESET}}$ and inputting the Block Protect command performs block protection. The first cycle of the command sequence is the Setup command. In the second cycle, the Block Protect command is input, in which a block address and $A1 = V_{IH}$ and $A0 = A6 = V_{IL}$ are input. At this time, the device writes to the block protector circuit. Until write is complete, there must be a wait of t_{PPLH} but the device need not be controlled during this time. In the third cycle, the Verify Block Protect command is input. This command verifies write to the block protector circuit. Read is performed in the fourth cycle. If the protection operation is complete, 01H is output. If other than 01H is output, write is not complete; thus, input the Block Protect command again. Canceling VID to $\overline{\text{RESET}}$ exits this mode.

Temporary Block Unprotection

The TC58VSF4682/4683AASB has a temporary block unprotection feature which disables block protection for all protected blocks. Unprotection is enabled by applying VID to the $\overline{\text{RESET}}$ pin. At this time, Write and Erase operations can be performed on all the blocks except the boot blocks protected by Boot Block Protect. The device returns to the previous condition after VID is removed from the $\overline{\text{RESET}}$ pin. That is, previously protected blocks are protected again.

Verify Block Protect

The Verify Block Protect command is used to ascertain whether a block is protected or unprotected. This mode is set by setting $A0, A6$ and the block address $A19 \sim A12$ to V_{IL} and setting $A1$ to V_{IH} . This command should be input before a Read operation is performed. 0001H is output if the block is protected and 0000H is output if the block is unprotected. In Byte Mode $DQ8$ to $DQ15$ are in High-Impedance state. Block protection verification can also be carried out using a software command.

Boot Block Protection

Boot Block Protection temporarily protects some boot blocks using a method other than ordinary block protection. VID or a command sequence is not required. Protection is performed simply by inputting V_{IL} to $\overline{\text{WP/ACC}}$. The target blocks are two of the boot blocks. The Top Boot Block uses $BA133/BA134$; the Bottom Boot Block, $BA0/BA1$. Inputting V_{IH} to $\overline{\text{WP/ACC}}$ releases the mode. At this time, the block is protected in ordinary block protection mode.

Hidden Rom Area

The TH50VSF4682/4683AASB features a 64-Kbyte Hidden ROM area apart from the memory cells. The area consists of one block. Data Read, Write, and Protect can be performed on the block. Because Protect cannot be released, once the block is protected, data in the block cannot be overwritten.

The Hidden ROM area is located in the address space indicated in the Hidden ROM Area Address Table. Normally, memory cell data are accessed. To access the Hidden ROM area, input a Hidden ROM mode Entry command. At this time, the device enters Hidden ROM mode, allowing Read, Write, Erase, and Block Protect. Write and Erase operations are the same as Auto operations except that the device is in Hidden ROM mode. However, regarding write operation, Acceleration mode can not be performed during Hidden ROM Mode. To protect the Hidden ROM area, use the Block Protect function. Operation of Block Protect here is the same as in normal Block Protect except that V_{IH} rather than V_{ID} is input to \overline{RESET} . Once the block is protected, protection cannot be released even using a Temporary Block Unprotect function. Use Block Protect carefully. Note that in Hidden ROM mode, simultaneous operation cannot be performed. Therefore, do not access areas other than the Hidden ROM area.

To exit Hidden ROM mode, use the Hidden ROM Mode Exit command. The device returns to Read mode.

Hidden Rom Area Address Table

TYPE	BOOT BLOCK ARCHITECTURE	BYTE MODE		WORD MODE	
		ADDRESS RANGE	SIZE	ADDRESS RANGE	SIZE
TH50VSF4682AASB	TOP BOOT BLOCK	7F0000H~7FFFFFFH	64 Kbytes	3F8000H~3FFFFFFH	32 Kwords
TH50VSF4683AASB	BOTTOM BOOT BLOCK	000000H~00FFFFFFH	64 Kbytes	000000H~007FFFFH	32 Kwords

Common Flash Memory Interface (CFI)

The TH50VSF4682/4683AASB conforms to the CFI. Information on device specifications and characteristics can be obtained via CFI. To read information from the device, input the Query command followed by the address. In Word mode, DQ8 to DQ15 all output 0s. To exit this mode, input the Reset command.

CFI Code Table

ADDRESS A6~A0	DATA DQ15~DQ0	DESCRIPTION
10H 11H 12H	0051H 0052H 0059H	Query Unique ASCII string "QRY"
13H 14H	0002H 0000H	Primary OEM Command Set 2: AMD/FJ standard type
15H 16H	0040H 0000H	Address for Primary Extended Table
17H 18H	0000H 0000H	Alternate OEM Command Set 0: none exists
19H 1AH	0000H 0000H	Address for Alternate OEM Extended Table
1BH	0027H	V _{DD} Min (write/erase) DQ7~DQ4: 1 V DQ3~DQ0: 100 mV
1CH	0036H	V _{DD} Max (write/erase) DQ7~DQ4: 1 V DQ3~DQ0: 100 mV
1DH	0000H	V _{PP} Min voltage
1EH	0000H	V _{PP} Max voltage
1FH	0004H	Typical timeout per single byte/word write (2 ^N μs)
20H	0000H	Typical timeout for Min size buffer write (2 ^N μs)
21H	000AH	Typical timeout per individual block erase (2 ^N ms)
22H	0000H	Typical timeout for full chip erase (2 ^N ms)
23H	0005H	Max timeout for byte/word write (2 ^N times typical)
24H	0000H	Max timeout for buffer write (2 ^N times typical)
25H	0004H	Max timeout per individual block erase (2 ^N times typical)
26H	0000H	Max timeout for full chip erase (2 ^N times typical)
27H	0017H	Device Size (2 ^N byte)
28H 29H	0002H 0000H	Flash Device Interface description 2: x8/x16
2AH 2BH	0000H 0000H	Max number of byte in multi-byte write (2 ^N)

ADDRESS A6~A0	DATA DQ15~DQ0	DESCRIPTION
2CH	0002H	Number of Erase Block Region within device
2DH	0007H	Erase Block Region 1 Information 0~15 bit: y = Block Number 16~31 bit: z = Block Size (z × 256 byte)
2EH	0000H	
2FH	0020H	
30H	0000H	
31H	007EH	Erase Block Region 2 Information
32H	0000H	
33H	0000H	
34H	0001H	
40H	0050H	Query Unique ASCII string "PRI"
41H	0052H	
42H	0049H	
43H	0031H	Major version number, ASCII
44H	0031H	Minor version number, ASCII
45H	0000H	Address Sensitive Unlock 0: Required 1: Not Required
46H	0002H	Erase Suspend 0: Not Supported 1: To Read Only 2: To Read & Write
47H	0001H	Block Protect 0: Not Supported X: Number of blocks in per group
48H	0001H	Block Temporary Unprotect 0: Not Supported 1: Supported
49H	0004H	Block Protect/Unprotect scheme
4AH	0001H	Simultaneous Operation 0: Not Supported 1: Supported
4BH	0000H	Burst Mode 0: Not Supported
4CH	0000H	Page Mode 0: Not Supported
4DH	0085H	V _{ACC} Min voltage DQ7~DQ4: 1 V DQ3~DQ0: 100 mV
4EH	0095H	V _{ACC} Max voltage DQ7~DQ4: 1 V DQ3~DQ0: 100 mV
4FH	000XH	Top/Bottom Boot Block Flag 2: TH50VSF4682AASB 3: TH50VSF4683AASB
50H	0001H	Program Suspend 0: Not Supported 1: Supported

HARDWARE SEQUENCE FLAGS FOR FLASH MEMORY

The TH50VSF4682/4683AASB has a Hardware Sequence flag which allows the device status to be determined during an auto mode operation. The output data is read out using the same timing as that used when $\overline{CE\overline{F}} = \overline{OE} = V_{IL}$ in Read Mode. The $\overline{RY/B\overline{Y}}$ output can be either High or Low.

The device re-enters Read Mode automatically after an auto mode operation has been completed successfully. The Hardware Sequence flag is read to determine the device status and the result of the operation is verified by comparing the read-out data with the original data.

DQ7 (\overline{DATA} polling)

During an Auto-Program or auto-erase operation, the device status can be determined using the data polling function. \overline{DATA} polling begins on the rising edge of \overline{WE} in the last bus cycle. In an Auto-Program operation, DQ7 outputs inverted data during the programming operation and outputs actual data after programming has finished. In an auto-erase operation, DQ7 outputs 0 during the erase operation and 1 when the erase operation has finished. If an auto mode operation fails, DQ7 simply outputs the data.

When the operation has finished, the address latch is reset. Data polling is asynchronous with the \overline{OE} signal.

DQ6 (Toggle bit 1)

The device status can be determined by the Toggle Bit function during an Auto Program or Auto Erase operation. The Toggle bit begins toggling on the rising edge of \overline{WE} in the last bus cycle. DQ6 alternately outputs a 0 or a 1 for each attempt (\overline{OE} access) while $\overline{CE\overline{F}} = V_{IL}$ while the device is busy. When the internal operation has been completed, toggling stops and valid memory cell data can be read by subsequent reading. If the operation failed, the DQ6 output toggles.

DQ6 toggles for around 3 μ s when an attempt is made to execute an Auto Program operation on a protected block. It then stops toggling. DQ6 toggles for around 100 μ s when an attempt is made to execute an Auto Erase operation on a protected block. It then stops toggling. After toggling stops the device returns to Read mode.

DQ5 (internal time-out)

DQ5 outputs a 1 when the Internal Timer has timed out during a Program or Erase operation. This indicates that the operation has not completed within the allotted time.

An attempt to program 1 into a cell containing 0 will fail (see Auto Program mode). DQ5 outputs 1 in this case. Either a hardware reset or a software reset command is required to put the device into Read mode.

DQ3 (Block Erase timer)

The Block Erase operation starts 50 μ s (Erase Hold Time) after the rising edge of \overline{WE} in the last command cycle. DQ3 outputs a 0 during the Block Erase Hold Time and a 1 when the Erase operation starts. Additional Block Erase commands can only be accepted during this Block Erase Hold Time. Each Block Erase command received within this hold time resets the timer, allowing additional blocks to be marked for erasing. DQ3 outputs a 1 if the Program or Erase operation fails.

DQ2 (Toggle bit 2)

DQ2 is used to detect blocks for Auto Block Erase or to detect whether the device is in Erase Suspend mode.

During Auto Block Erase, if data are continuously read from the selected block, DQ2 output toggles. At this time 1 is output from non-selected blocks; thus, the selected block can be detected. When the device is in Erase Suspend mode, if data are continuously read from the selected block for Auto Block Erase, DQ2 output toggles. At this time, because DQ6 output does not toggle, Erase Suspend mode can be detected. When the device is in Programming mode during Erase suspend, if data are read from the address to which data are being written, DQ2 outputs 1.

RY/ \overline{BY} (READY / \overline{BUSY})

The TH50VSF4682/4683AASB has a RY/ \overline{BY} signal to indicate the device status to the host processor. A 0 (Busy state) indicates that an Auto Program or Auto Erase operation is in progress. A 1 (Ready state) indicates that the operation has finished and that the device can accept a new command. The RY/ \overline{BY} signal outputs a 0 when an operation has failed.

The RY/ \overline{BY} signal outputs a 0 after the rising edge of \overline{WE} in the last command cycle.

During an Auto Block Erase operation, commands other than Erase Suspend are ignored. The RY/ \overline{BY} signal outputs a 1 during an Erase Suspend operation. The output buffer for the RY/ \overline{BY} pin is an open drain type circuit, allowing a wired — OR connection. A pull-up resistor needs to be inserted between VCC and the RY/ \overline{BY} pin.

DATA PROTECTION

The TH50VSF4682/4683AASB features a function which makes malfunction or data damage difficult.

Protection Against Program/Erase Caused by Low Supply Voltage

To prevent malfunction at power on or power down, the device does not receive commands when V_{CCf} is below V_{LKO} . In this state, command input is ignored.

If V_{CCf} drops below V_{LKO} during Auto operations, the device terminates Auto Program execution. In this case, Auto operation is not executed again when V_{CCf} return to recommended V_{CCf} voltage Therefore, command need to be input to execute Auto operation again.

When $V_{CCf} > V_{LKO}$, make up countermeasure to be input accurately command in system side please.

Protection Against Malfunction Caused by Glitches

To prevent malfunction caused by noise from the system in operation, the device does not receive pulses shorter than 3 ns(Typ.) input to \overline{WE} , \overline{CEF} , or \overline{OE} . However, if a glitch exceeding 3 ns(Typ.) occurs and the glitch is input to the device, although rare, malfunction may occur.

The device uses standard JEDEC commands; thus making command input difficult. It is conceivable that in an extreme case a part of a command sequence input due to system noise may occur. At this time, the device acknowledges the part of the command sequence. Then, even if the proper command is input, the device does not operate. To avoid this, before command input, clear the Command register. In an environment where system noise occurs easily, Toshiba recommends input of a software or hardware reset before command input.

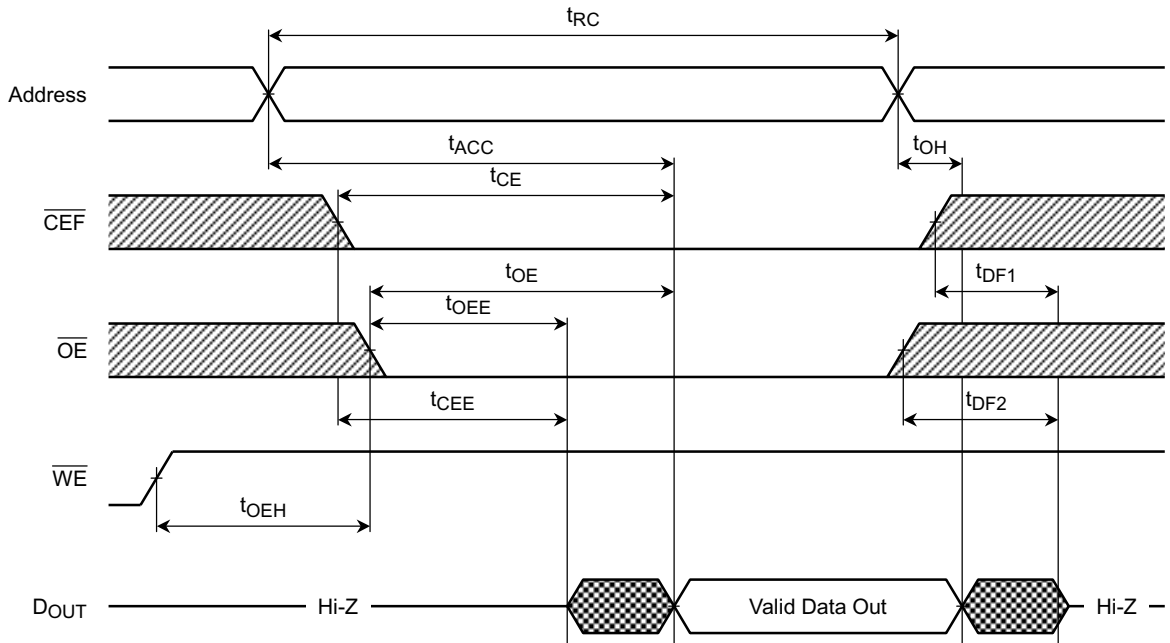
Protection Against Malfunction at Power-on

To prevent damage to data caused by sudden noise at power on, when power is turned on with $\overline{WE} = \overline{CEF} = V_{IL}$, the device does not latch the command at the first rising edge of \overline{WE} or \overline{CEF} . The device automatically resets the Command register and enters Read mode.

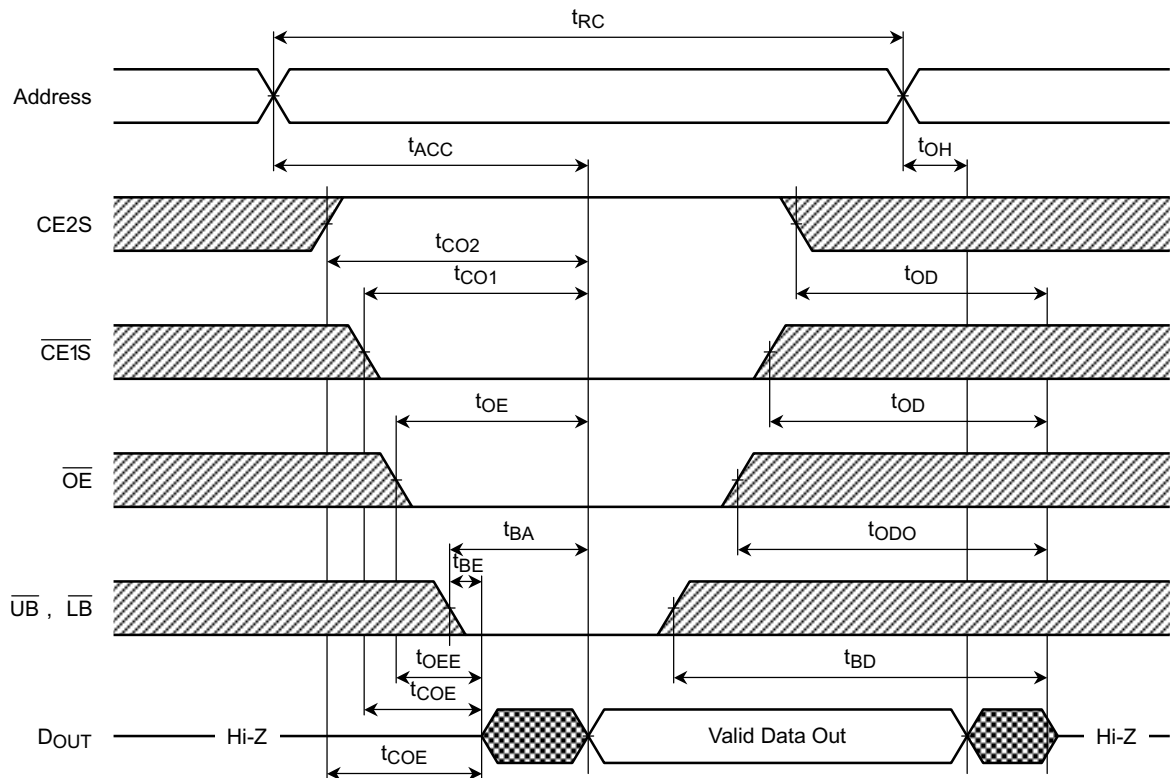
TIMING DIAGRAMS



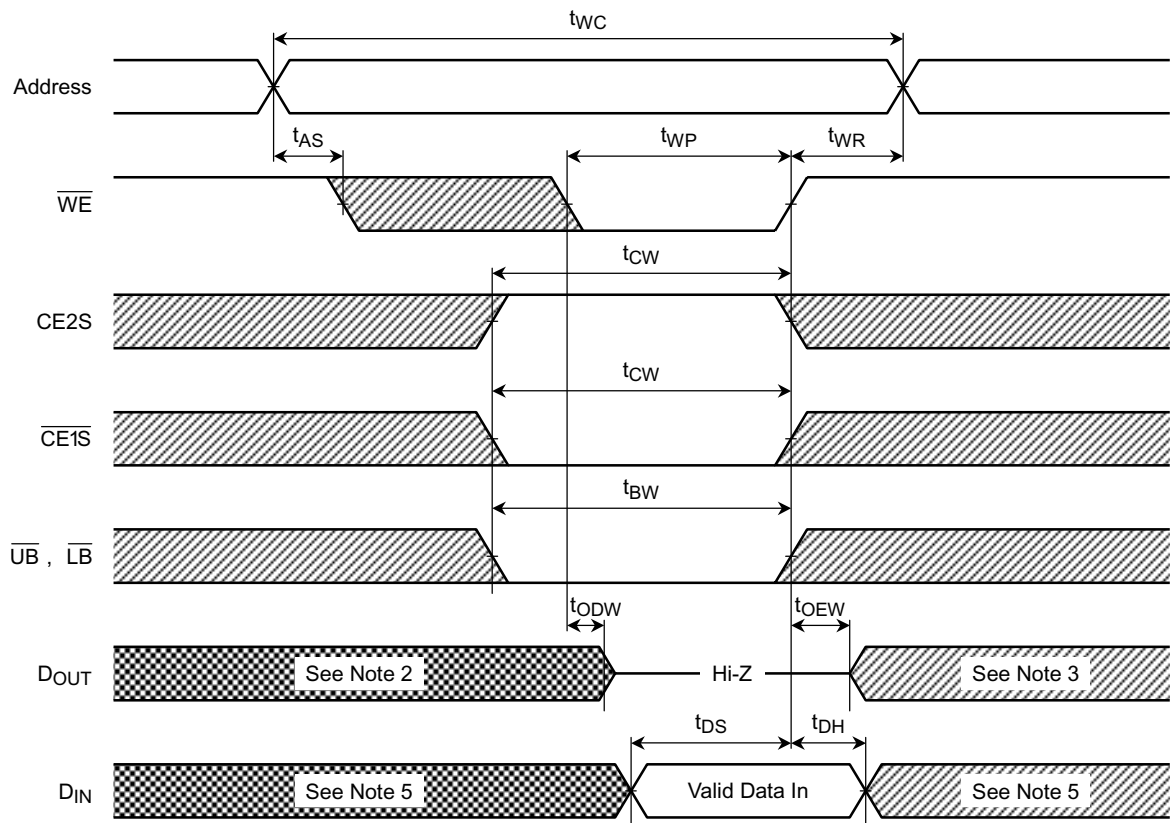
FLASH READ/ID READ OPERATION



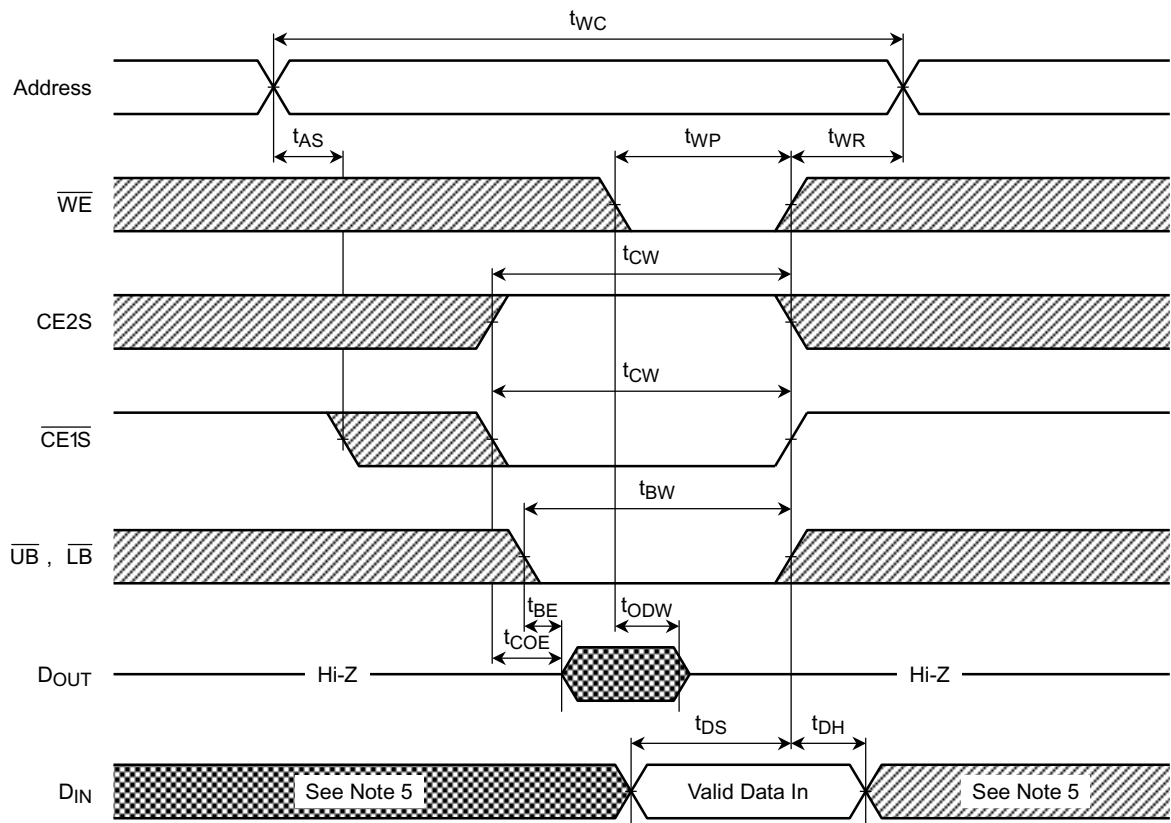
SRAM READ CYCLE (see Note 1)



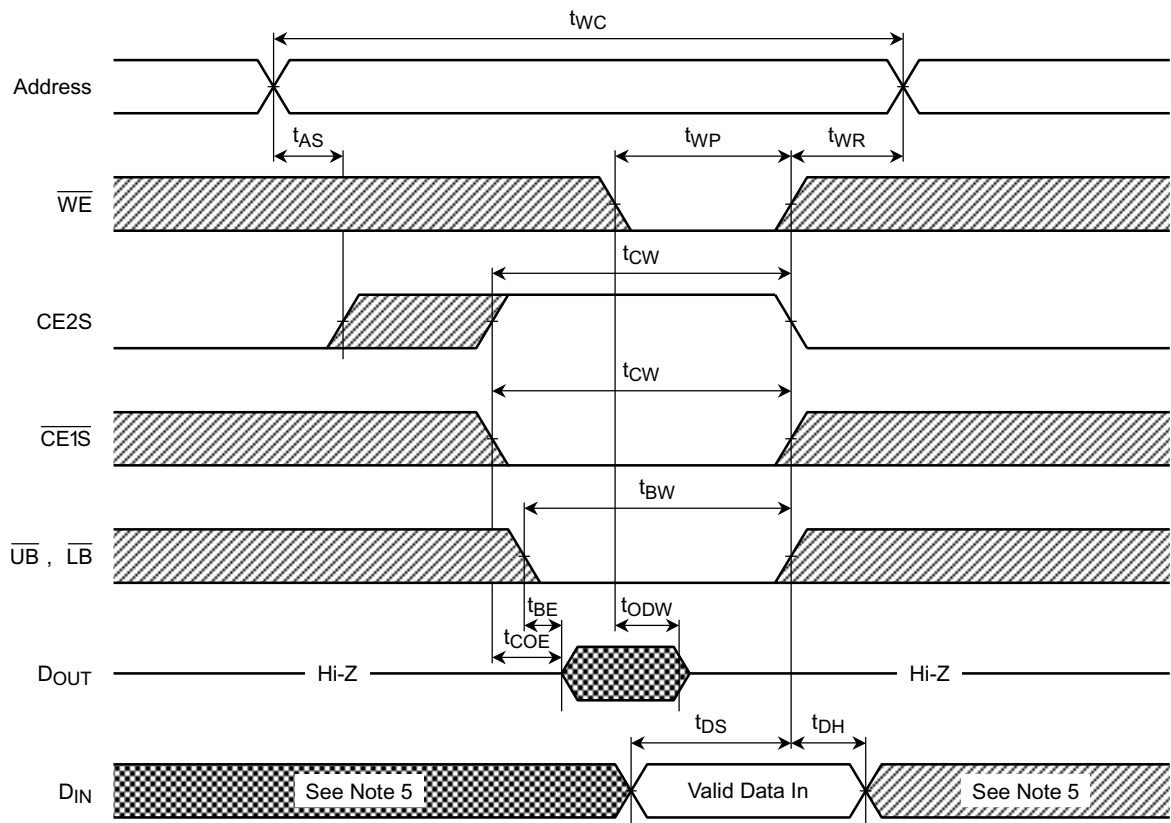
SRAM WRITE CYCLE 1 (\overline{WE} -CONTROLLED) (see Note 4)



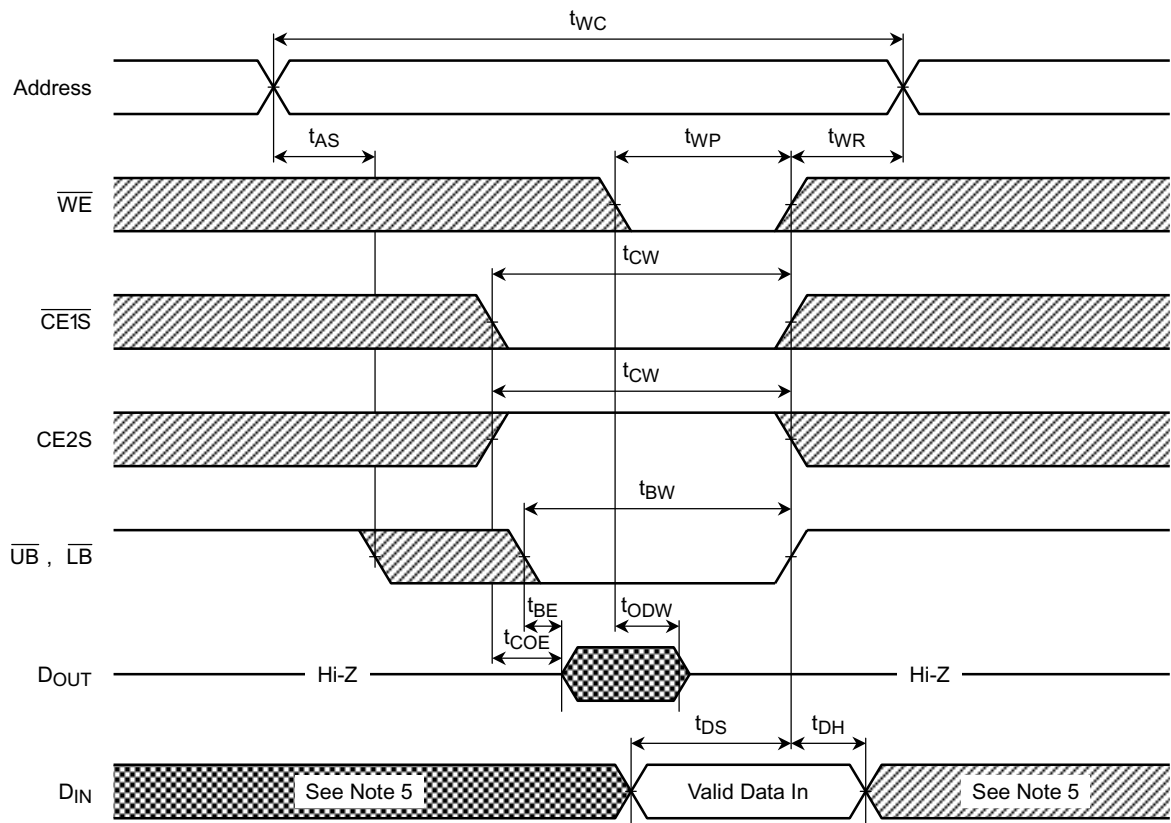
SRAM WRITE CYCLE 2 ($\overline{CE1S}$ -CONTROLLED) (see Note 4)



SRAM WRITE CYCLE 3 (CE2S-CONTROLLED) (see Note 4)



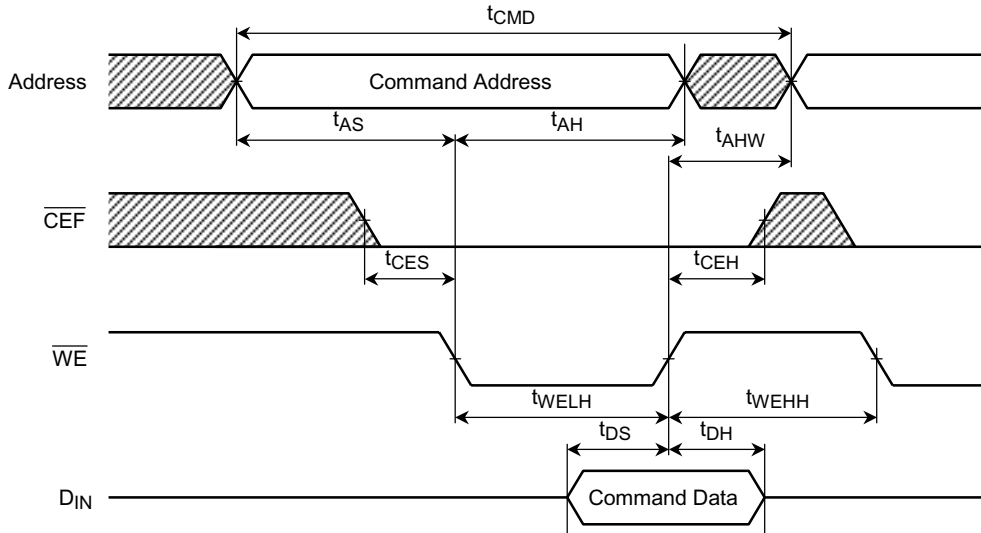
SRAM WRITE CYCLE 4 (\overline{UB} - and \overline{LB} -CONTROLLED) (see Note 4)



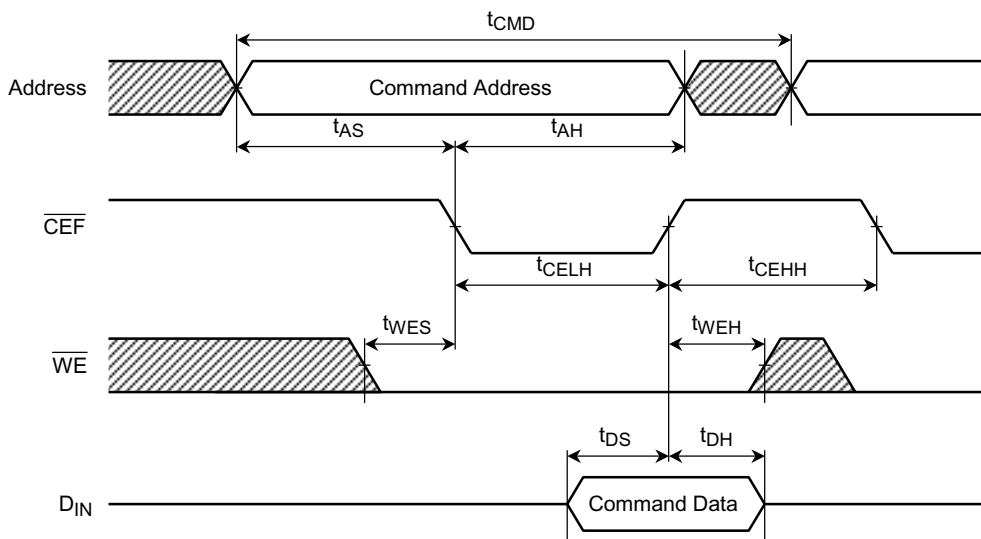
FLASH COMMAND WRITE OPERATION

This is the timing of the Command Write Operation. The timing which described follow pages is typically same as this page's.

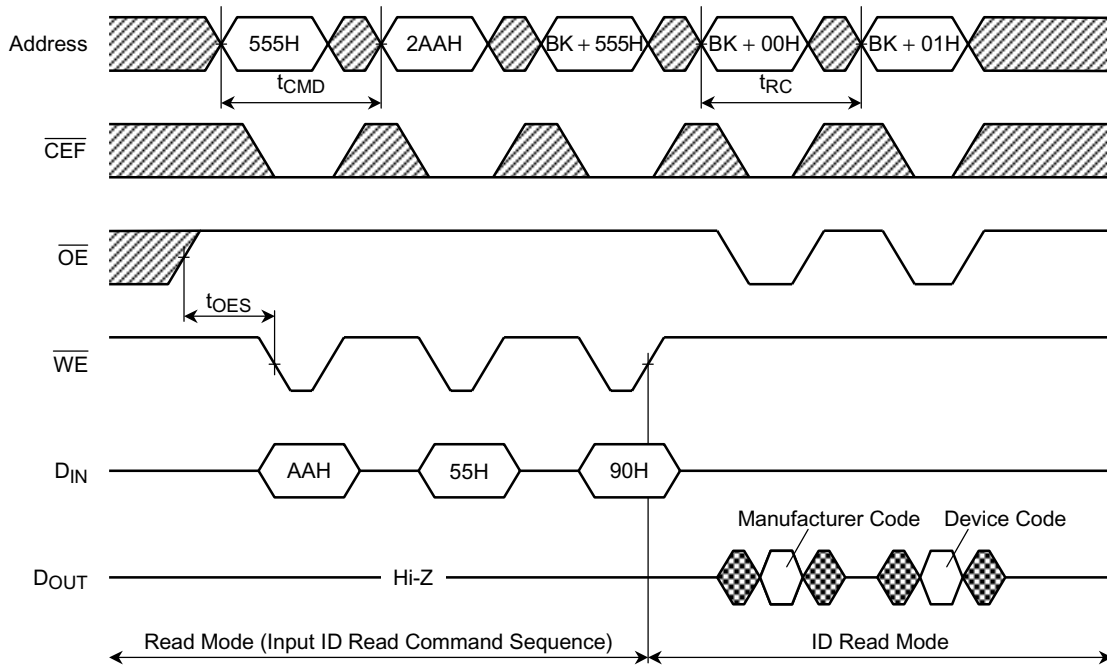
- \overline{WE} Control



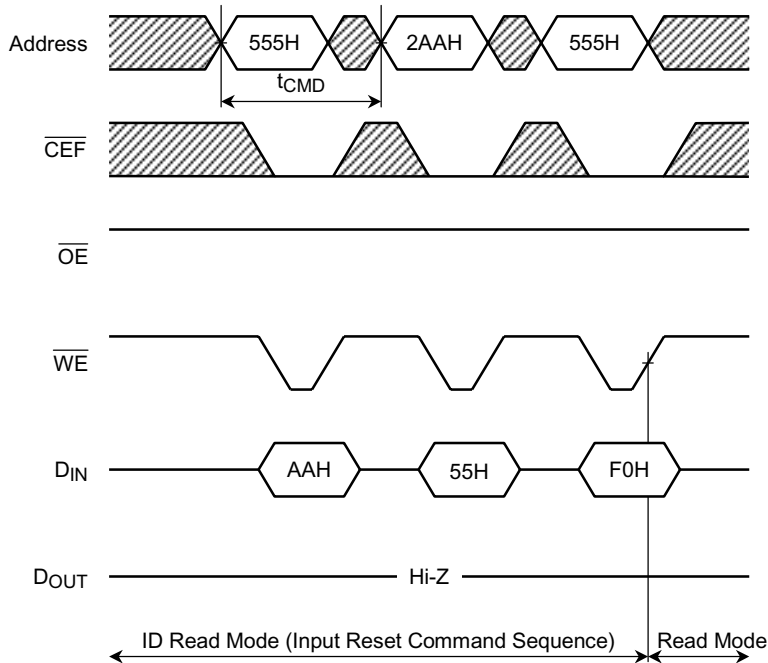
- \overline{CE} Control



FLASH ID READ OPERATION (Input command sequence)

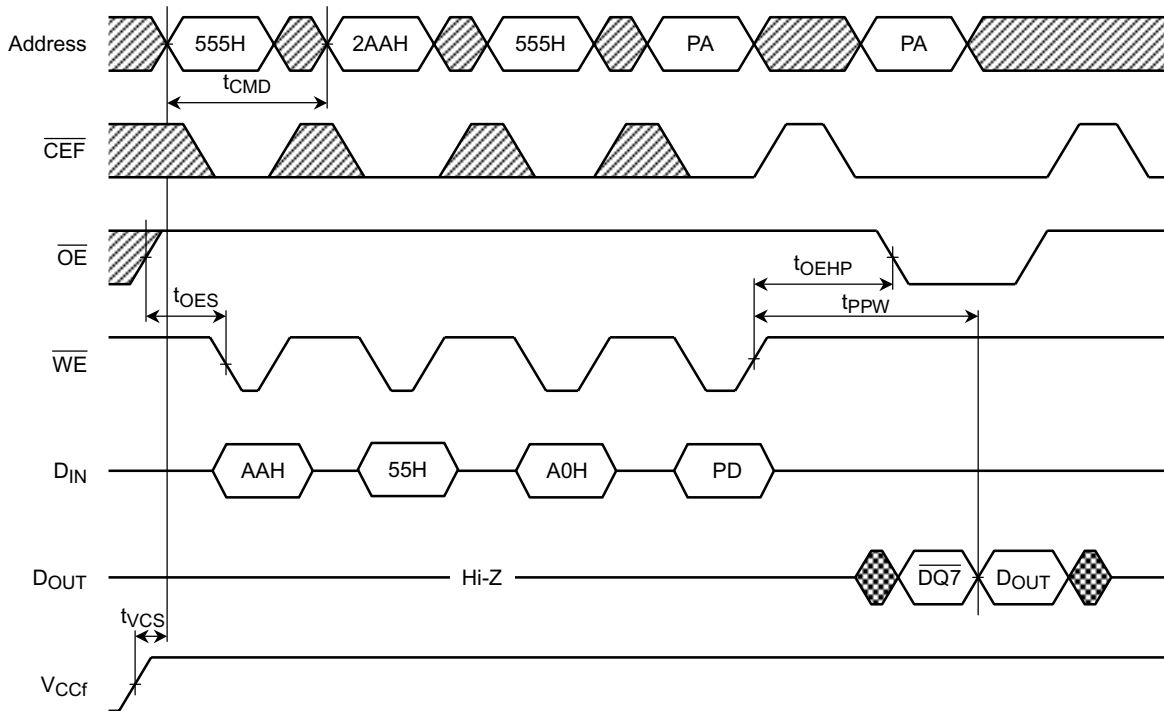


(Continued)



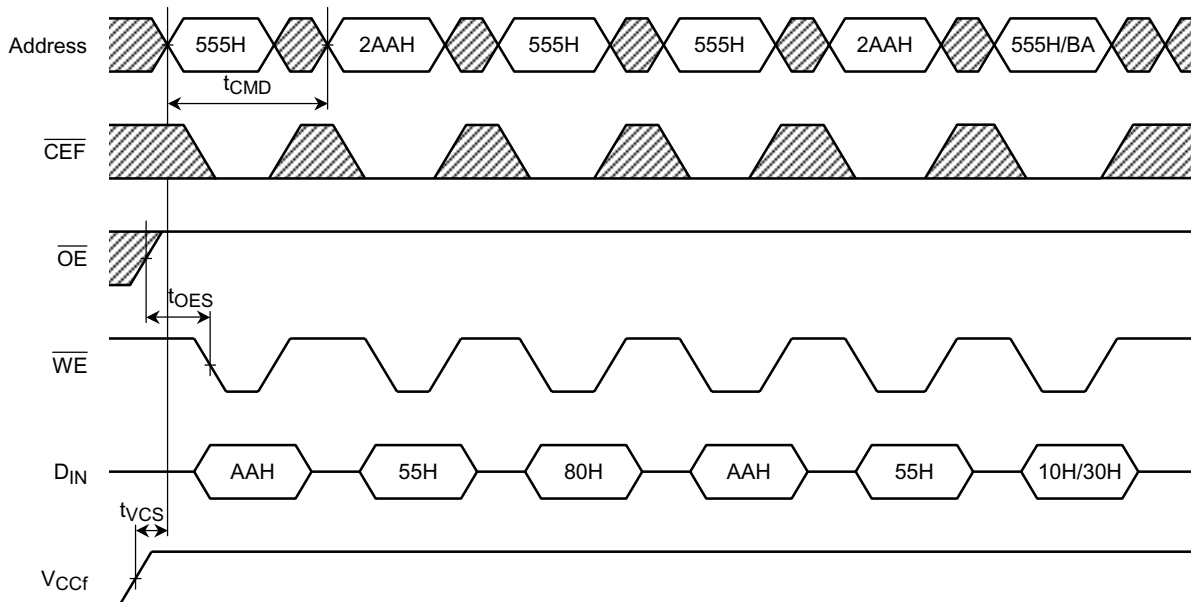
Notes: Word mode address shown
BK: Bank address

FLASH AUTO-PROGRAM OPERATION (\overline{WE} -CONTROLLED)



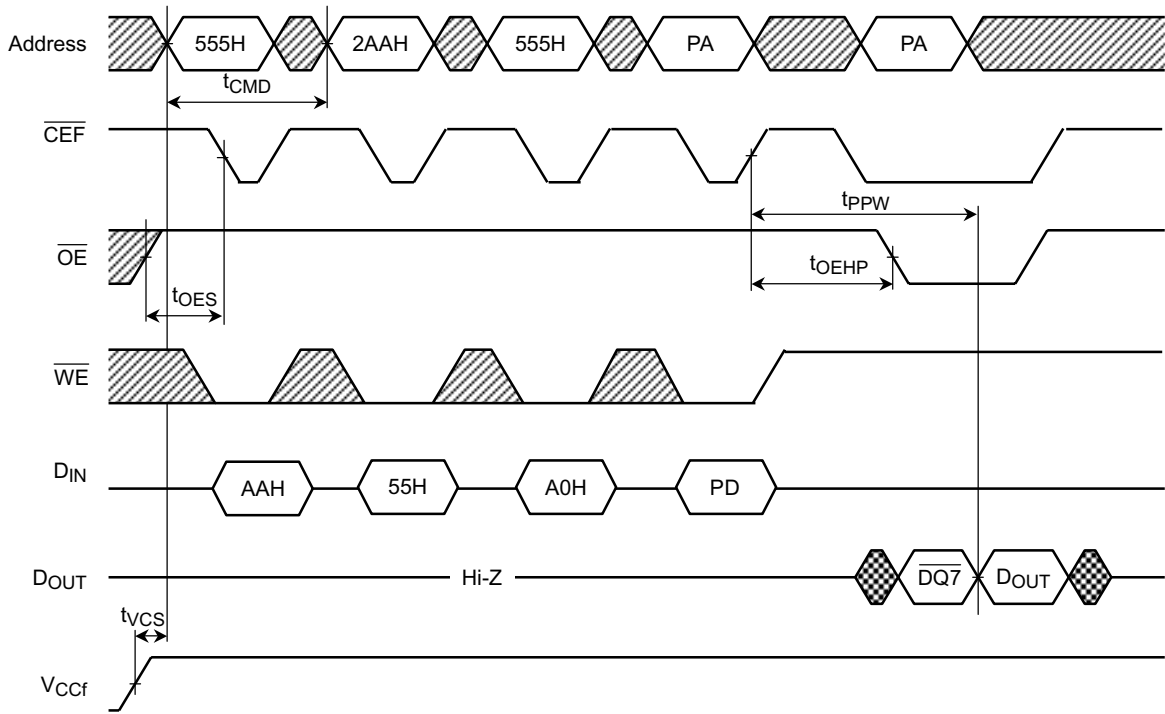
Note: Word Mode address shown.
 PA: Program address
 PD: Program data

FLASH AUTO CHIP ERASE/AUTO BLOCK ERASE OPERATION (\overline{WE} -CONTROLLED)



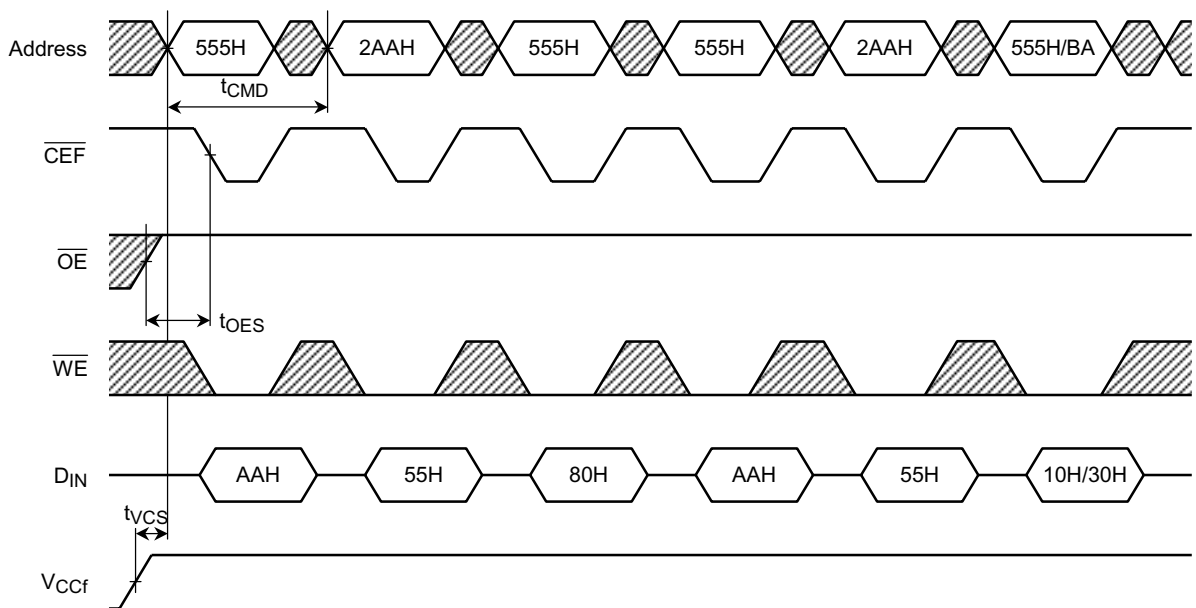
Notes: Word mode address shown
 BA: Block address for Auto Block Erase operation

FLASH AUTO-PROGRAM OPERATION ($\overline{\text{CE}}\overline{\text{F}}$ -CONTROLLED)



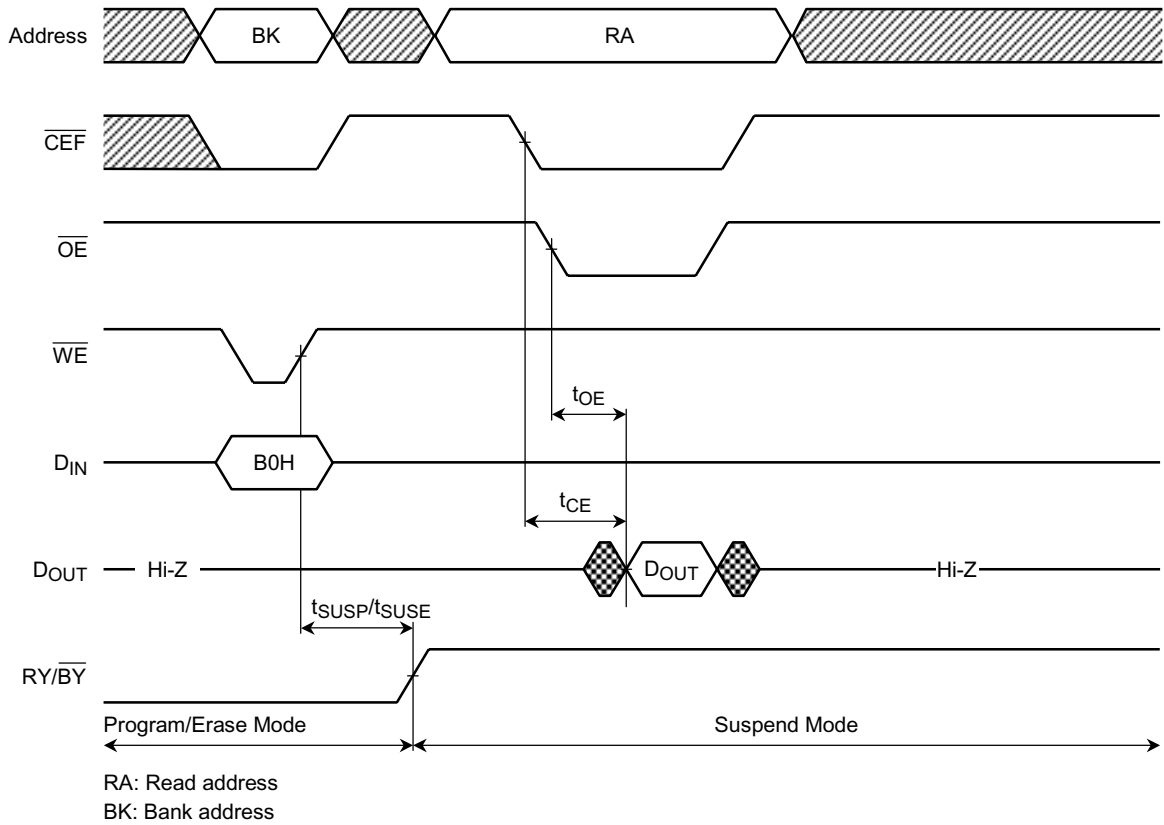
Notes: Word mode address shown
 PA: Program address
 PD: Program data

FLASH AUTO CHIP ERASE/AUTO BLOCK ERASE OPERATION ($\overline{\text{CE}}\overline{\text{F}}$ -CONTROLLED)

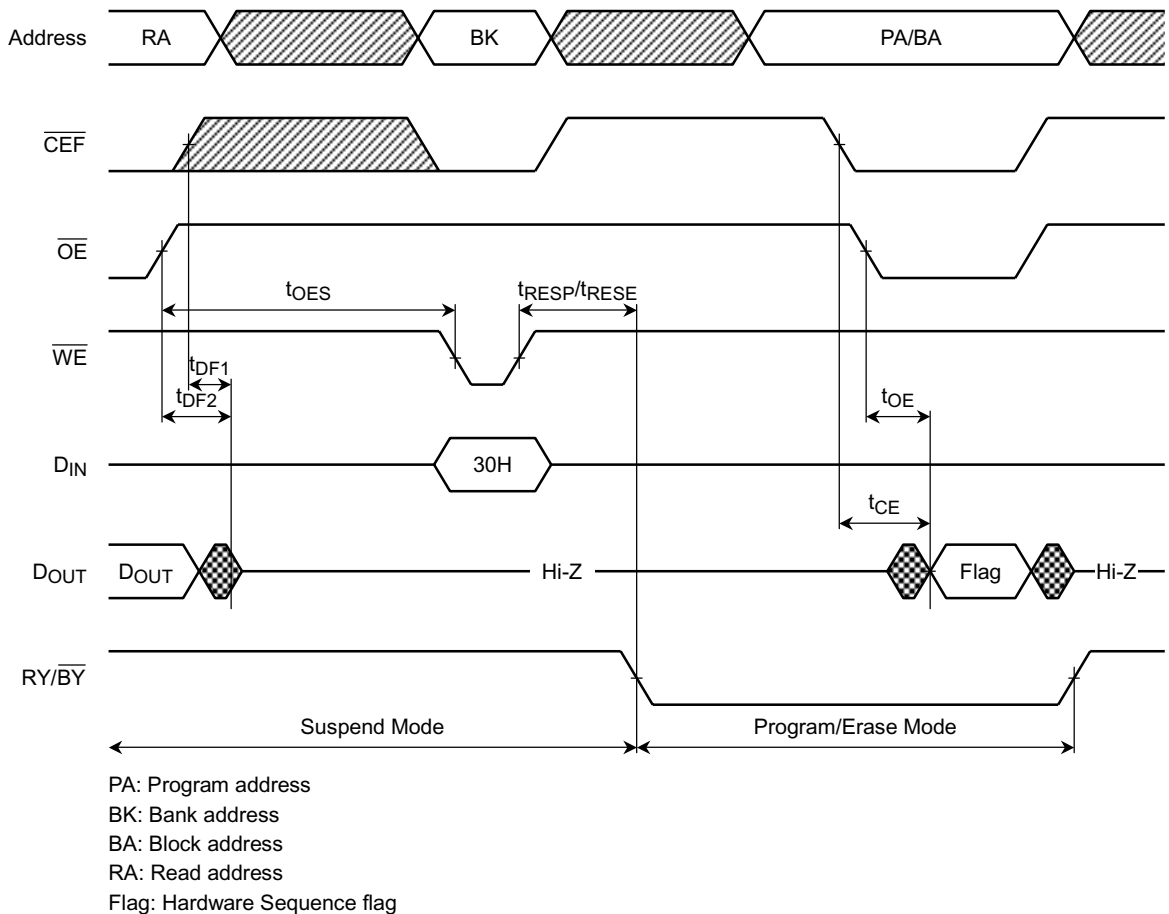


Notes: Word mode address shown
 BA: Block address for Auto Block Erase operation

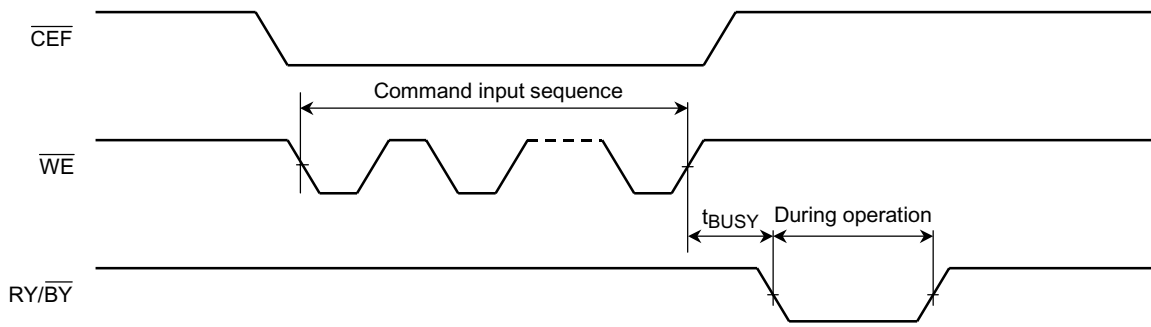
FLASH PROGRAM/ERASE SUSPEND OPERATION



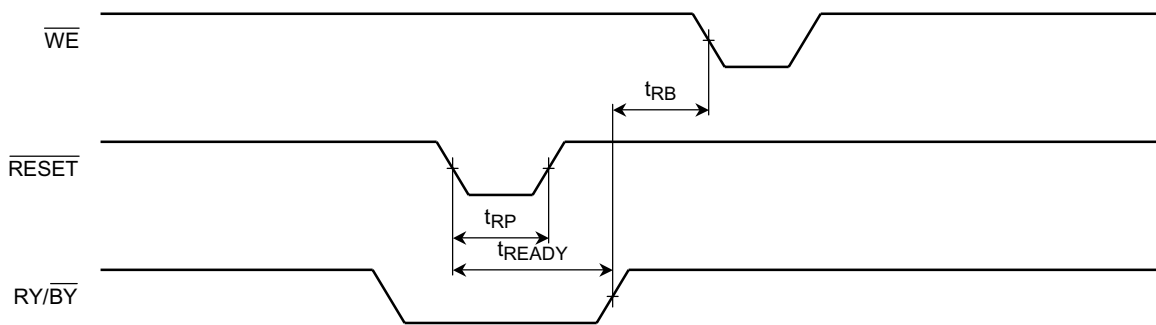
FLASH PROGRAM/ERASE RESUME OPERATION



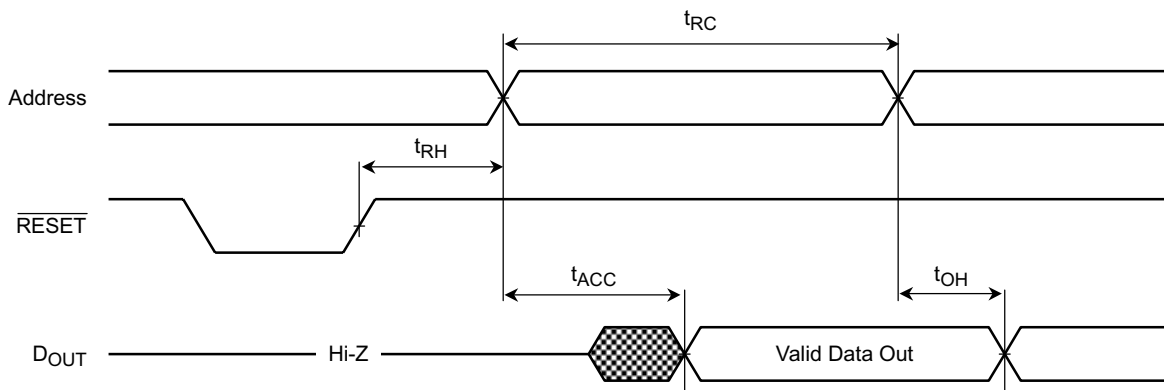
FLASH RY/ $\overline{\text{BY}}$ DURING AUTO-PROGRAM/ERASE OPERATION



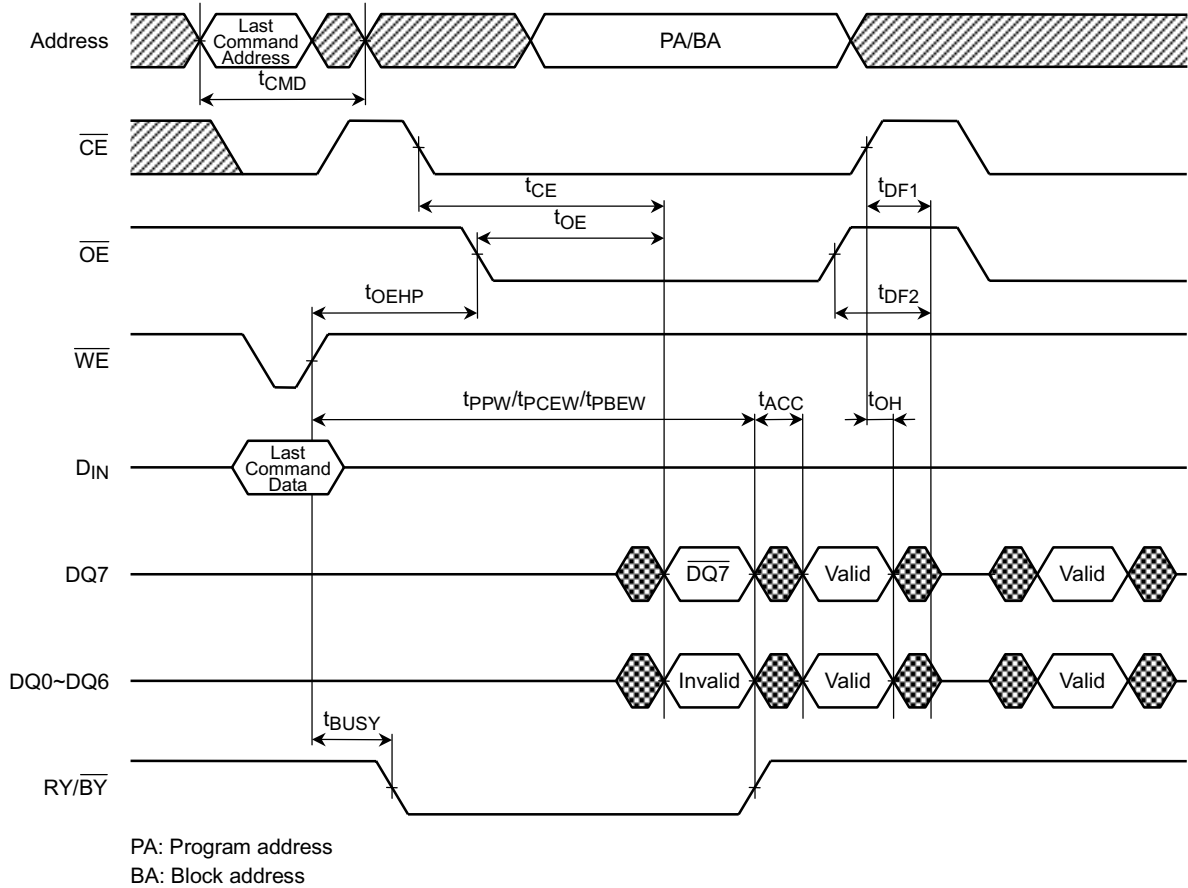
FLASH HARDWARE RESET OPERATION



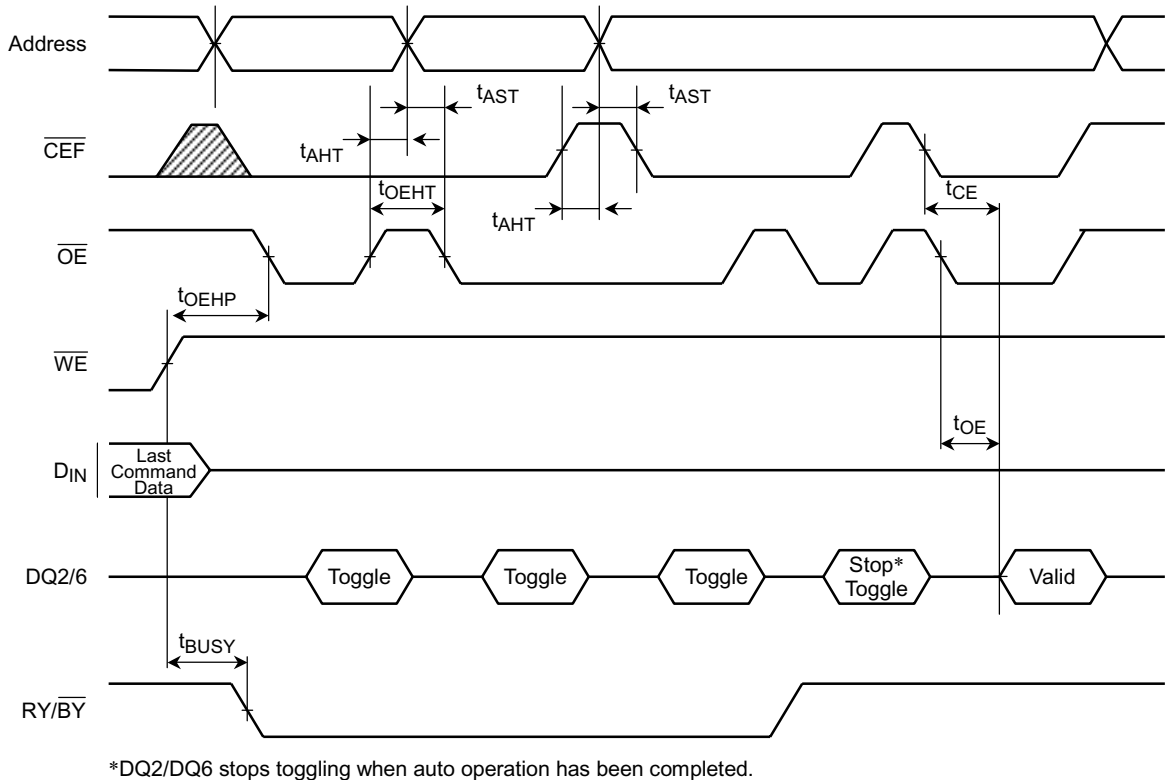
FLASH READ AFTER $\overline{\text{RESET}}$



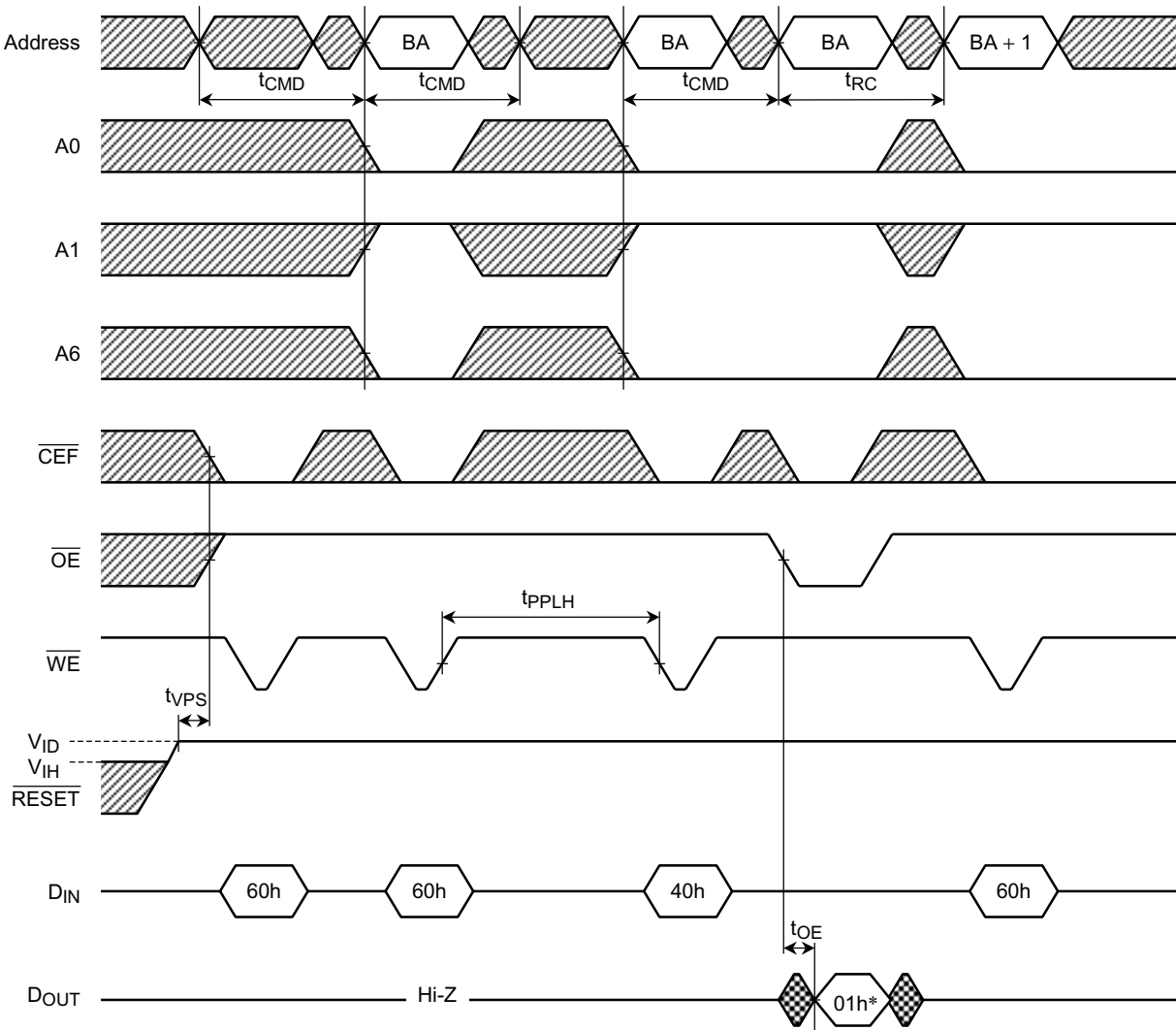
FLASH HARDWARE SEQUENCE FLAG (DATA Polling)



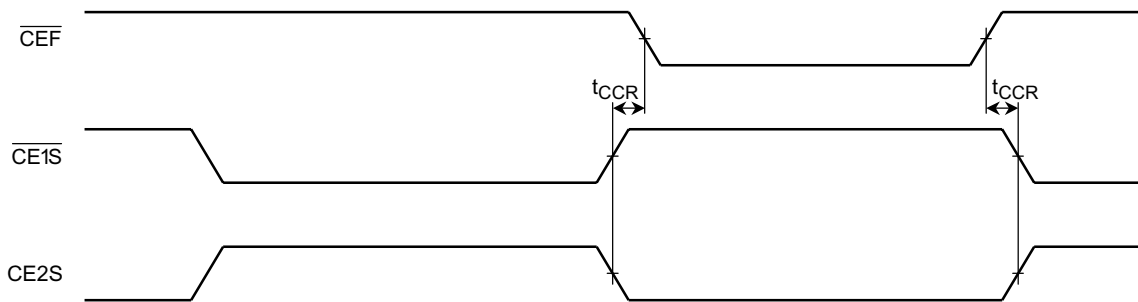
FLASH HARDWARE SEQUENCE FLAG (Toggle Bit)



FLASH BLOCK PROTECT OPERATION



Notes: BA : Block address
 BA + 1: Next Block address
 * : 01h indicates that block is protected.

TIMING FOR SWITCHING BETWEEN FLASH AND SRAM MODES

Notes:

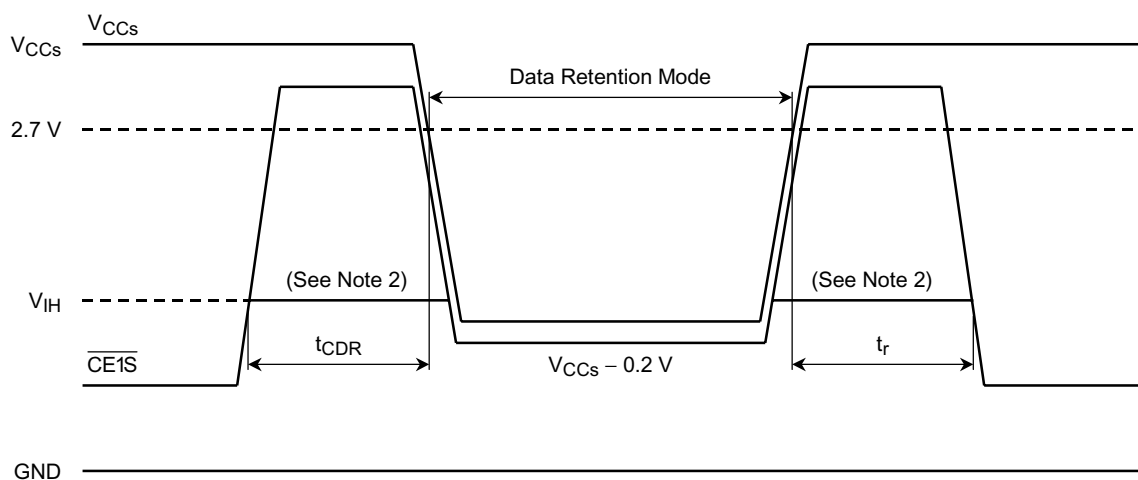
- (1) \overline{WE} remains High during a Read cycle.
- (2) If $\overline{CE1\overline{S}}$ goes Low (or $CE2\overline{S}$ goes High) at the same time as or after \overline{WE} goes Low, the outputs will remain High-Impedance.
- (3) If $\overline{CE1\overline{S}}$ goes High (or $CE2\overline{S}$ goes Low) at the same time as or before \overline{WE} goes High, the outputs will remain High-Impedance.
- (4) If \overline{OE} is High during a Write cycle, the outputs will remain High-Impedance.
- (5) Because I/O pins may be in Output state at this point, input signals of the opposite value must not be applied.
- (6) DOUT6 stops toggling when the last command has been completed.

SRAM DATA RETENTION CHARACTERISTICS (Ta = -30~85°C)

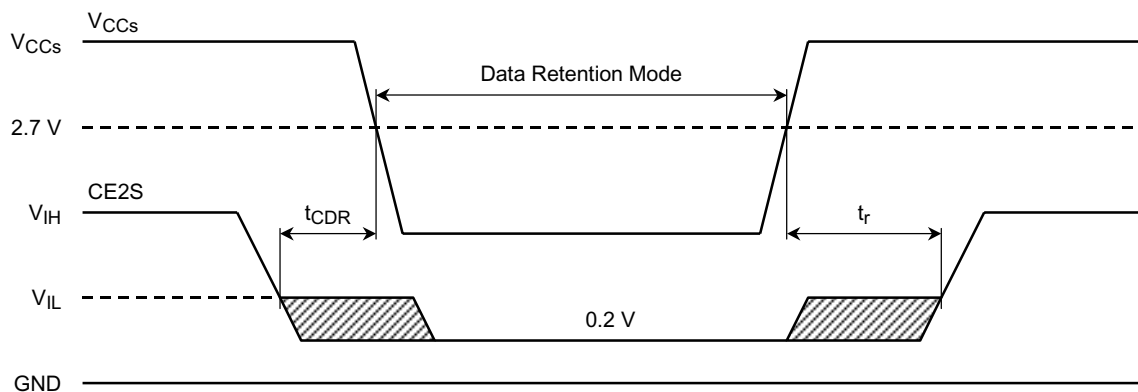
SYMBOL	PARAMETER		MIN	TYP.	MAX	UNIT
V _{DH}	Data Retention Supply Voltage for SRAM		1.5	—	3.1	V
I _{CCS4}	SRAM Standby Current	V _{DH} = 3.1 V Ta = -30~85°C	—	—	10	μA
		V _{DH} = 3.0 V	Ta = -30~40°C	—	1	
			Ta = -30~85°C	—	5	
t _{CDR}	Chip-Deselect-to-Data-Retention-Mode Time		0	—	—	ns
t _r	Recovery Time		t _{RC} ⁽¹⁾	—	—	ns

(1) Read cycle time

CE1S-CONTROLLED DATA RETENTION MODE (see Note 1, 4)



CE2S-CONTROLLED DATA RETENTION MODE (see Note 3)

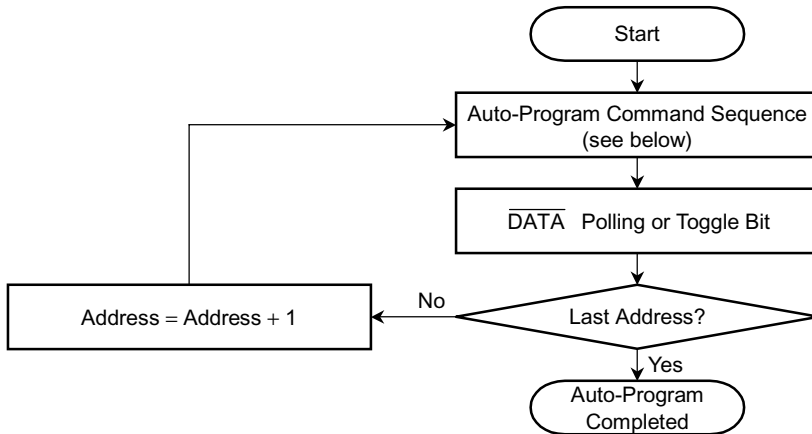


Notes:

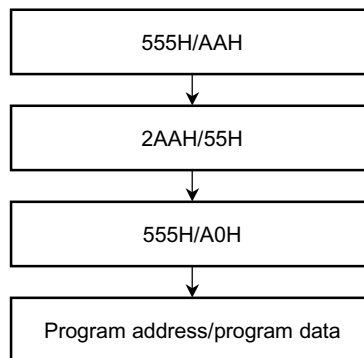
- (1) In $\overline{\text{CE1S}}$ -Controlled Data Retention Mode, Minimum Standby Current Mode is entered when $\text{CE2S} \leq 0.2 \text{ V}$ or $\text{CE2S} \geq \text{VCCs} - 0.2 \text{ V}$.
- (2) When $\overline{\text{CE1S}}$ is operating at the VIH level, the SRAM standby current is the same as ICCS3 during the transition of VCCs from 3.1 V to 2.4 V.
- (3) In CE2S -Controlled Data Retention Mode, Minimum Standby Current Mode is entered when $\text{CE2S} \leq 0.2 \text{ V}$.
- (4) In $\overline{\text{UB}} / \overline{\text{LB}}$ controlled data retention mode, minimum standby current mode is entered when $\overline{\text{CE1S}} / \text{CE2S} \leq 0.2 \text{ V}$ or $\overline{\text{CE1S}} / \text{CE2S} \geq \text{VCCs} - 0.2 \text{ V}$.

FLOWCHARTS OF FLASH MEMORY OPERATIONS

Auto-Program

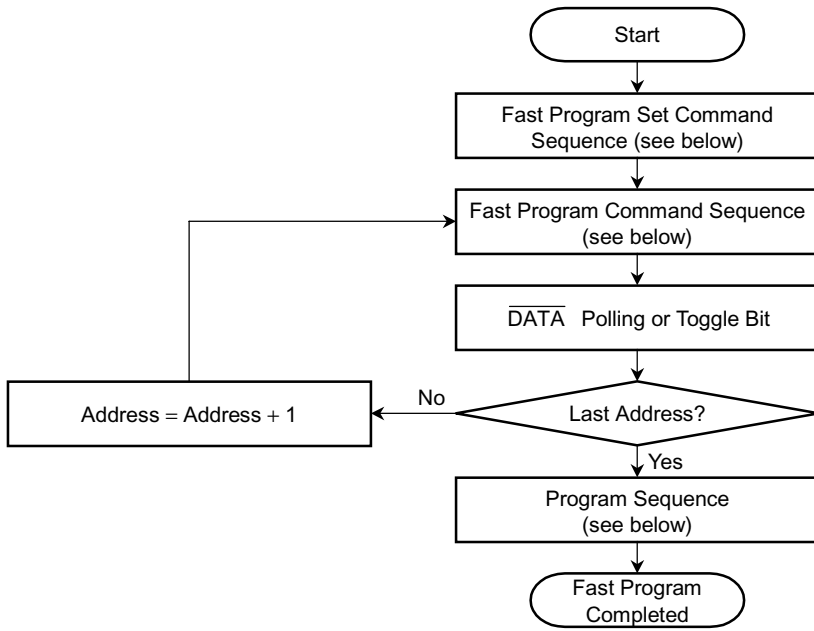


Auto-Program command sequence (address/data)

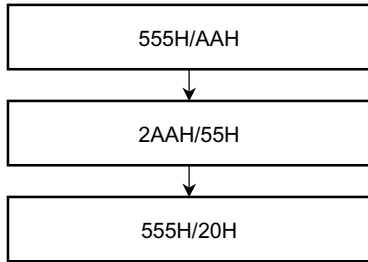


Note: Word mode command sequence is shown.

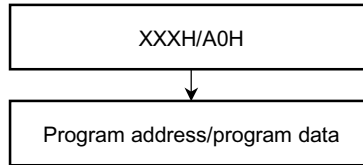
Fast Program



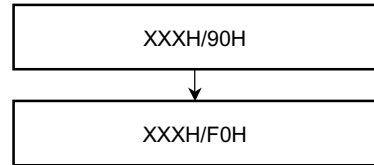
Fast Program Set command sequence (address/data)



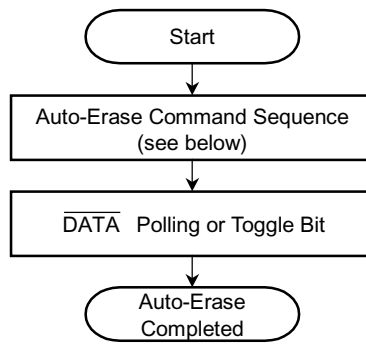
Fast Program command sequence (address/data)



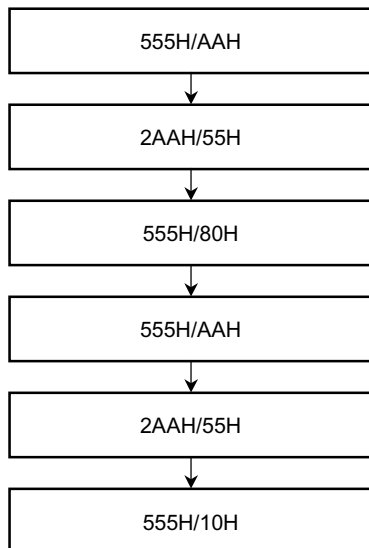
Fast Program Reset command sequence (address/data)



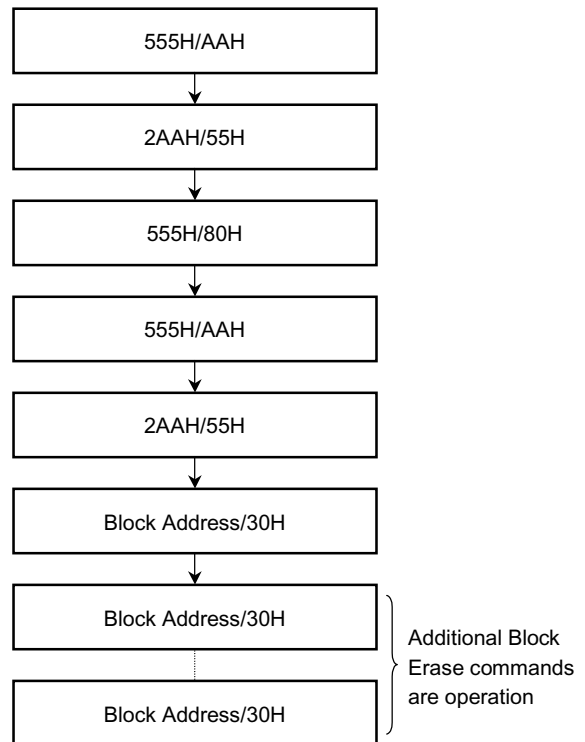
Auto-Erase



Auto Chip Erase command sequence
(address/data)

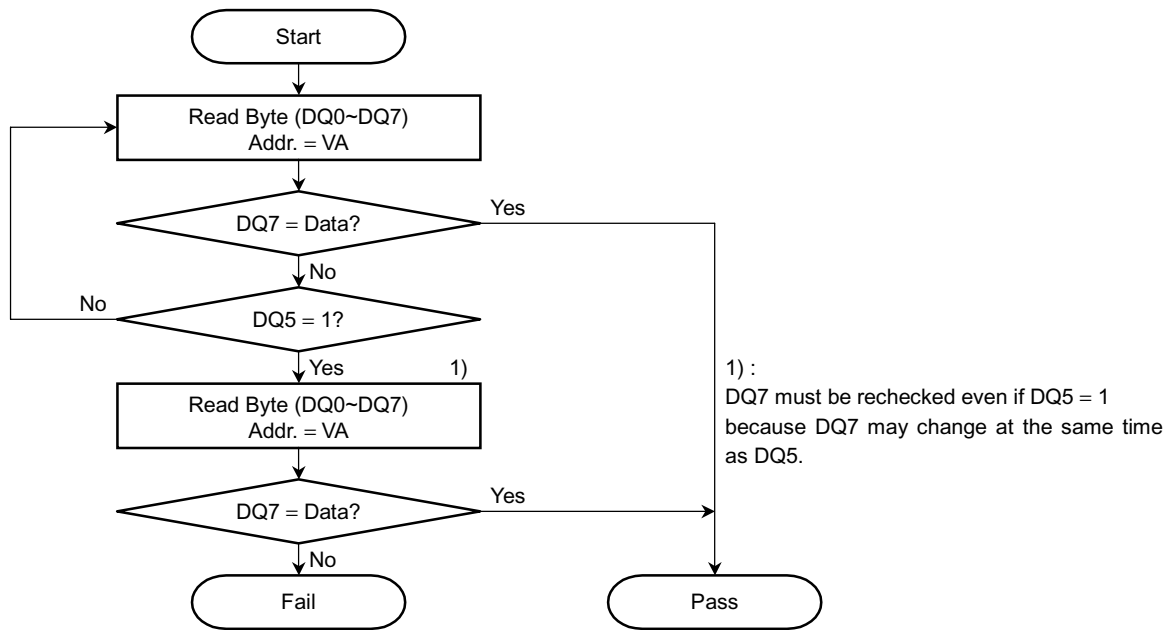


Auto Block Erase / Multiple-Block Erase command
sequence (address/data)

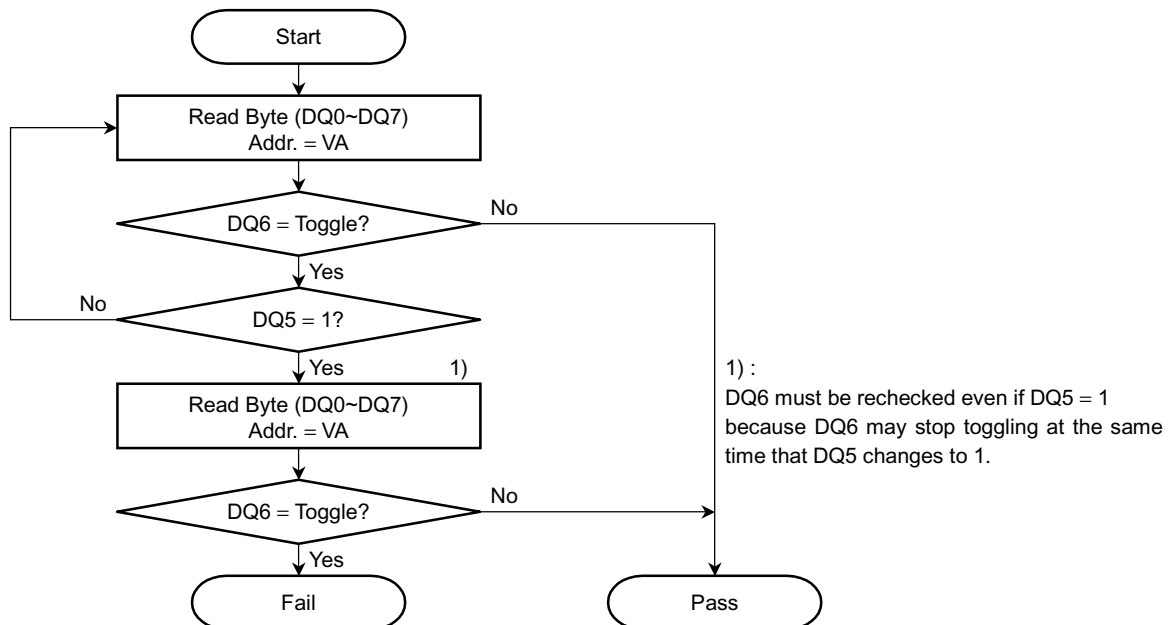


Note: Word mode command sequence is shown.

DQ7 ($\overline{\text{DATA}}$ Polling)



DQ6 (Toggle bit)



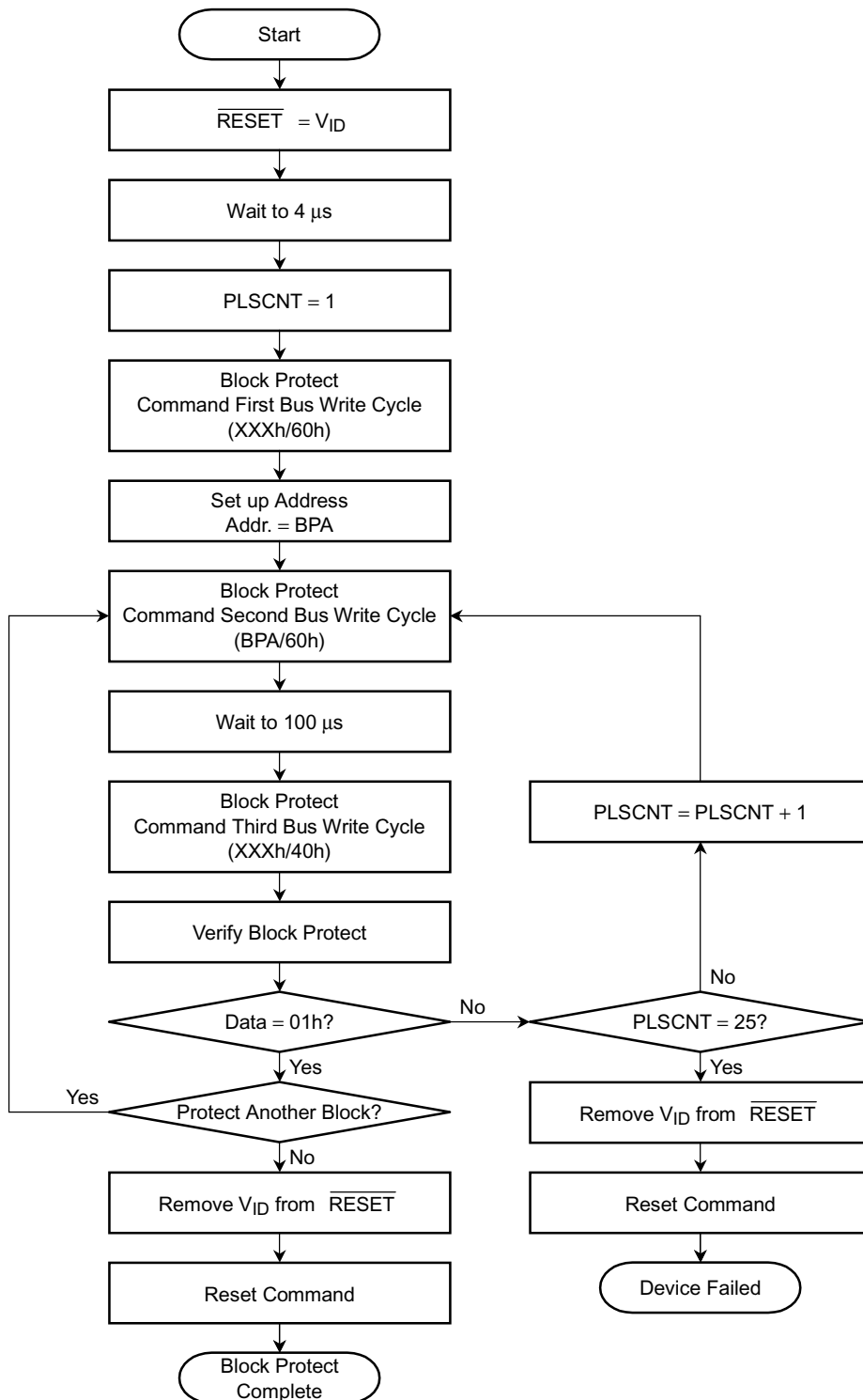
VA: Byte address for programming.

Any of the addresses within the block being erased during a Block Erase operation.

Don't care during a Chip Erase operation.

Any address not within the current block during an Erase Suspend operation.

Block Protect



BPA: Block Address and ID Read Address (A6, A1, A0)
 ID Read Address = (0, 1, 0)

PACKAGE DIMENSIONS

Unit: mm

P-FBGA69-1012-0.80A3(A)

